

# 16Mb B-die Page NOR Specification

**INFORMATION IN THIS DOCUMENT IS PROVIDED IN RELATION TO SAMSUNG PRODUCTS, AND IS SUBJECT TO CHANGE WITHOUT NOTICE.**

**NOTHING IN THIS DOCUMENT SHALL BE CONSTRUED AS GRANTING ANY LICENSE, EXPRESS OR IMPLIED, BY ESTOPPEL OR OTHERWISE,**

**TO ANY INTELLECTUAL PROPERTY RIGHTS IN SAMSUNG PRODUCTS OR TECHNOLOGY. ALL INFORMATION IN THIS DOCUMENT IS PROVIDED**

**ON AS "AS IS" BASIS WITHOUT GUARANTEE OR WARRANTY OF ANY KIND.**

1. For updates or additional information about Samsung products, contact your nearest Samsung office.
2. Samsung products are not intended for use in life support, critical care, medical, safety equipment, or similar applications where Product failure could result in loss of life or personal or physical harm, or any military or defense application, or any governmental procurement to which special terms or provisions may apply.

\* Samsung Electronics reserves the right to change products or specification without notice.

**Document Title**

***16M Bit (1M x16) Page Mode / Multi-Bank NOR Flash Memory***

**Revision History**

<b><u>Revision No.</u></b>	<b><u>History</u></b>	<b><u>Draft Date</u></b>	<b><u>Remark</u></b>
0.0	Initial draft	May 17, 2007	Target Information
0.1	Fast Initail Access Time 55ns is deleted.	July 03, 2007	Target Information
1.0	Qualified	July 05, 2007	

# K8P1615UQB

# FLASH MEMORY

## 16M Bit (1M x16) Page Mode / Multi-Bank NOR Flash Memory

### FEATURES

- Single Voltage, 2.7V to 3.6V for Read and Write operations  
Voltage range of 2.7V to 3.1V valid for MCP product
- Organization  
1M x16 bit (Word mode Only)
- Fast Read Access Time : 60ns
- Page Mode Operation  
8 Words Page access allows fast asynchronous read  
Page Read Access Time : 20ns
- Read While Program/Erase Operation
- Multiple Bank architectures (4 banks)  
Bank 0: 2Mbit (4Kw x 8 and 32Kw x 3)  
Bank 1: 6Mbit (32Kw x 12)  
Bank 2: 6Mbit (32Kw x 12)  
Bank 3: 2Mbit (4Kw x 8 and 32Kw x 3)
- OTP Block : Extra 256 word  
- 128word for factory and 128word for customer OTP
- Power Consumption (typical value)  
- Active Read Current : 45mA (@10MHz)  
- Program/Erase Current : 17mA  
- Read While Program or Read While Erase Current : 35mA  
- Standby Mode/Auto Sleep Mode : 15uA
- Support Single & Quad word accelerate program
- WP/ACC input pin  
- Allows special protection of two outermost boot blocks at V<sub>IL</sub>, regardless of block protect status  
- Removes special protection of two outermost boot block at V<sub>IH</sub>, the two blocks return to normal block protect status  
- Accelerated Quadword Program time : 1.5us
- Erase Suspend/Resume
- Program Suspend/Resume
- Unlock Bypass Program
- Hardware RESET Pin
- Command Register Operation
- Block Protection / Unprotection
- Supports Common Flash Memory Interface
- Operation Temperature Range  
- Industrial Temperature : -40°C to 85°C  
- Extended Temperature : -25°C to 85°C  
- Commercial Temperature : 0°C to 70°C

- Endurance : TBD
- Vio options at 1.8V and 3V I/O
- Package options  
- 48 Pin TSOP (20x12mm)  
- 48 Ball FBGA (6x8mm, 0.8mm Ball Pitch)

### GENERAL DESCRIPTION

The K8P1615UQB featuring single 3.0V power supply, is a 16Mbit NOR-type Flash Memory organized as 1Mx16. The memory architecture of the device is designed to divide its memory arrays into 46 blocks with independent hardware protection. This block architecture provides highly flexible erase and program capability. The K8P1615UQB NOR Flash consists of four banks. This device is capable of reading data from one bank while programming or erasing in the other banks.

The K8P1615UQB offers fast page access time of 20~30ns with random access time of 60~70ns. The device's fast access times allow high speed microprocessors to operate without wait states. The device performs a program operation in unit of 16 bits (Word) and erases in units of a block. Single or multiple blocks can be erased. The block erase operation is completed within typically 0.7 sec. The device requires 17mA as program/erase current in the commercial and industrial temperature ranges.

The K8P1615UQB NOR Flash Memory is created by using Samsung's advanced CMOS process technology. This device is available in 48 Pin TSOP package and 48 Ball FBGA package. The device is compatible with EPROM applications to require high-density and cost-effective non-volatile read/write storage solutions.

### PIN DESCRIPTION

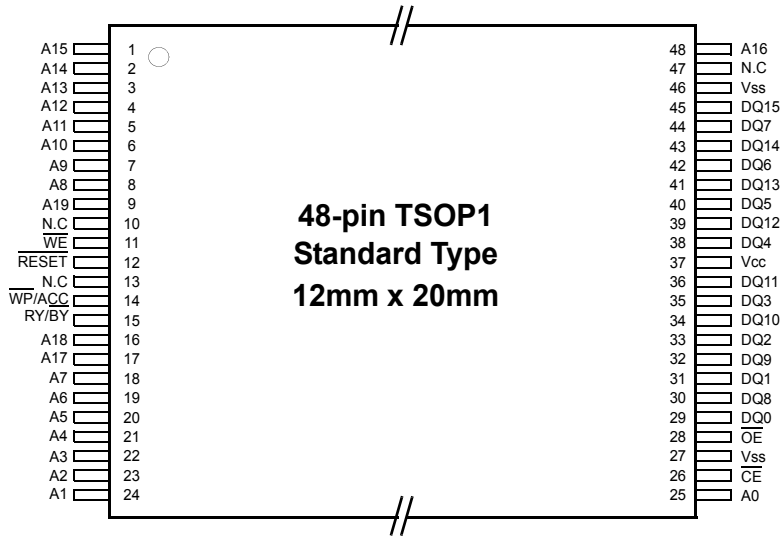
Pin Name	Pin Function
A0 - A19	Address Inputs
DQ0 - DQ15	Data Inputs / Outputs
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
$\overline{RESET}$	Hardware Reset Pin
RY/ $\overline{BY}$	Ready/Busy Output
$\overline{WE}$	Write Enable
WP/ACC	Hardware Write Protection/Program Acceleration
Vcc	Power Supply
Vss	Ground
N.C	No Connection

SAMSUNG ELECTRONICS CO., LTD. reserves the right to change products and specifications without notice.

**K8P1615UQB**

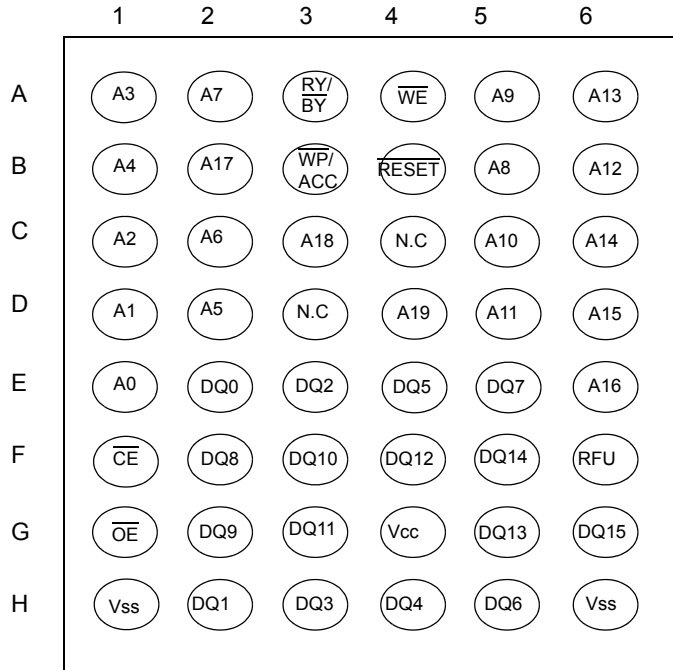
**FLASH MEMORY**

**PIN CONFIGURATION**



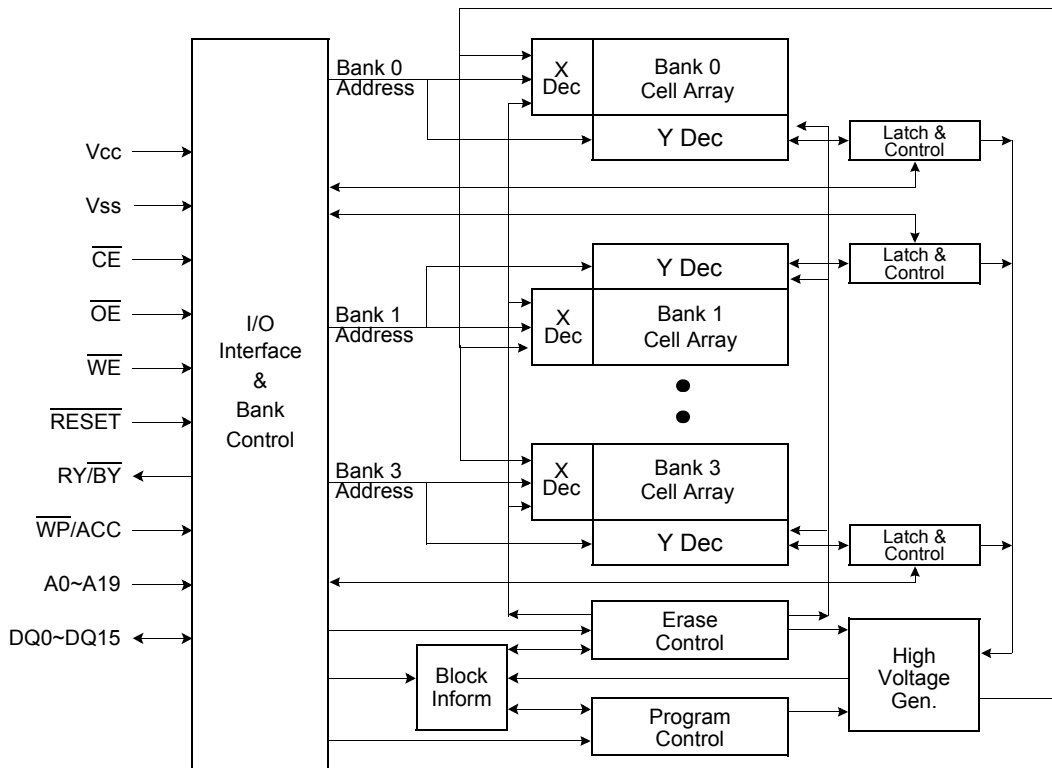
**K8P1615UQB**

**FLASH MEMORY**



**48 Ball FBGA TOP VIEW (BALL DOWN)**

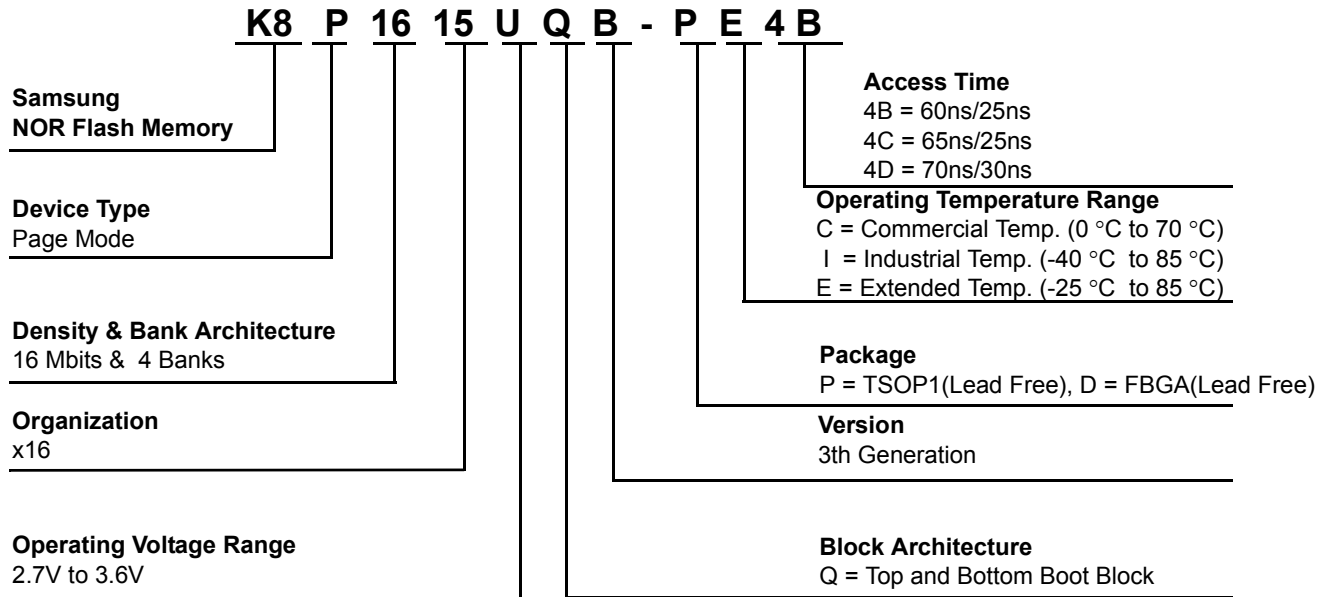
**FUNCTIONAL BLOCK DIAGRAM**



**K8P1615UQB**

**FLASH MEMORY**

**ORDERING INFORMATION**



**Table 1. PRODUCT LINE-UP**

Speed Item	Speed Option		
	4B	4C	4D
Vcc	2.7V~3.6V		
VIO (1)	1.65~1.95V , 2.7~3.6V		
Max. Address Access Time (ns)	60ns	65ns	70ns
Max. $\overline{CE}$ Access Time (ns)	60ns	65ns	70ns
Max. $\overline{OE}$ Access Time (ns)	25ns	25ns	30ns
Max. Page Access Time (ns)	25ns	25ns	30ns

**Notes :**  
1. Only 4C or 4D speed options can be provided in case of using 1.65~1.95V V<sub>IO</sub>.

**Table 2. K8P1615UQB DEVICE BANK DIVISIONS**

Bank 0, Bank 3		Bank 1, Bank 2	
Mbit	Block Sizes	Mbit	Block Sizes
2 Mbit	4 Kw x 8 and 32 Kw x 3	6 Mbit	32 Kw x 12

**Table 3. OTP BLOCK**

OTP	Block Address A19~A8	Area	Block Size	Address Range
	0000h	Factory-Locked Area	128 words	000000h-00007Fh
		Customer-Locked Area	128 words	000080h-0000FFh

After entering OTP block, any issued addresses should be in the range of OTP block address

Table 4. K8P1615UQB DEVICE BANK DIVISIONS

Bank	Number of Blocks	Block Size
0	8	4 Kwords
	3	32 Kwords
1	12	32 Kwords
2	12	32 Kwords
3	3	32 Kwords
	8	4 Kwords

**PRODUCT INTRODUCTION**

The K8P1615UQB is a 16Mbit NOR-type Flash memory. The device features single voltage power supply operating within the range of 2.7V to 3.6V. The device is programmed by using the Channel Hot Electron (CHE) injection mechanism which is used to program EPROMs. The device is erased electrically by using Fowler-Nordheim tunneling mechanism. To provide highly flexible erase and program capability, the device adapts a block memory architecture that divides its memory array into 46 blocks (4 Kw x 16 , 32 Kw x 30). Programming is done in units of 16 bits (Word). All bits of data in one or multiple blocks can be erased simultaneously when the device executes the erase operation. To prevent the device from accidental erasing or over-writing the programmed data, 46 memory blocks can be hardware protected. The device offers fast page access time of 20~30ns with random access time of 60~70ns supporting high speed microprocessors to operate without any wait states.

The command set of K8P1615UQB is fully compatible with standard Flash devices. The device is controlled by chip enable ( $\overline{CE}$ ), output enable ( $\overline{OE}$ ) and write enable ( $\overline{WE}$ ). Device operations are executed by selective command codes. The command codes to be combined with addresses and data are sequentially written to the command registers using microprocessor write timing. The command codes serve as inputs to an internal state machine which controls the program/erase circuitry. Register contents also internally latch addresses and data necessary to execute the program and erase operations. The K8P1615UQB is implemented with Internal Program/Erase Algorithms to execute the program/erase operations. The Internal Program/Erase Algorithms are invoked by program/erase command sequences. The Internal Program Algorithm automatically programs and verifies data at specified addresses. The Internal Erase Algorithm automatically pre-programs the memory cell which is not programmed and then executes the erase operation. The K8P1615UQB has means to indicate the status of completion of program/erase operations. The status can be indicated via the  $\overline{RY/BY}$  pin,  $\overline{Data}$  polling of DQ7, or the Toggle bit (DQ6). Once the operations have been completed, the device automatically resets itself to the read mode.

**Table 5. Operations Table**

Operation	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	WP/ACC	A9	A6	A1	A0	DQ8/DQ15	DQ0/DQ7	$\overline{RESET}$
Read	L	L	H	L/H	A9	A6	A1	A0	DOUT	DOUT	H
Stand-by	H	X	X	(2)	X	X	X	X	High-Z	High-Z	(2)
Output Disable	L	H	H	L/H	X	X	X	X	High-Z	High-Z	H
Reset	X	X	X	L/H	X	X	X	X	High-Z	High-Z	L
Write	L	H	L	(4)	A9	A6	A1	A0	DIN	DIN	H
Enable Block Protect (3)	L	H	L	L/H	X	L	H	L	X	DIN	V <sub>ID</sub>
Enable Block Unprotect (3)	L	H	L	(4)	X	H	H	L	X	DIN	V <sub>ID</sub>
Temporary Block Unprotect	X	X	X	(4)	X	X	X	X	X	X	V <sub>ID</sub>
Auto Select Manufacturer ID (5)	L	L	H	L/H	V <sub>ID</sub>	L	L	L	X	Code(See Table 7)	H
Auto Select Device Code (5)	L	L	H	L/H	V <sub>ID</sub>	L	L	H	X	Code(See Table 7)	H

**Notes :**

1. L = V<sub>IL</sub> (Low), H = V<sub>IH</sub> (High), V<sub>ID</sub> = 8.5V to 9.5V, D<sub>IN</sub> = Data in, D<sub>OUT</sub> = Data out, X = Don't care.
2.  $\overline{WP/ACC}$  and  $\overline{RESET}$  pin are asserted at V<sub>cc</sub>±0.2 V or V<sub>ss</sub>±0.2 V in the Stand-by mode.
3. Addresses must be composed of the Block address (A12 - A19).  
The Block Protect and Unprotect operations may be implemented via programming equipment too. Refer to the "Block Protection and Unprotection".
4. If  $\overline{WP/ACC}$ =V<sub>IL</sub> the two outermost boot blocks is protected. If  $\overline{WP/ACC}$ =V<sub>IH</sub>, the two outermost boot block protection depends on whether those blocks were last protected or unprotected using the method described in "Block Protection and Unprotection". If  $\overline{WP/ACC}$ =V<sub>IH</sub>, all blocks will be temporarily unprotected.
5. Manufacturer and device codes may also be accessed via a command register write sequence. Refer to Table 7.



**K8P1615UQB**

**FLASH MEMORY**

**COMMAND DEFINITIONS**

The K8P1615UQB operates by selecting and executing its operational modes. Each operational mode has its own command set. In order to select a certain mode, a proper command with specific address and data sequences must be written into the command register. Writing incorrect information which include address and data or writing an improper command will reset the device to the read mode. The defined valid register command sequences are stated in Table 6. Note that Erase Suspend (B0H) and Erase Resume (30H) commands are valid only while the Block Erase Operation is in progress. Program Suspend (B0H) and Program Resume (30H) commands are valid during Program Operation and Erase Suspend - Program Operation. Only Read Operation is available after Program Suspend Operation.

**Table 6. Command Sequences**

Command Sequence		Cycle	1st Cycle	2nd Cycle	3rd Cycle	4th Cycle	5th Cycle	6th Cycle
Read	Addr	1	RA					
	Data		RD					
Reset	Addr	1	XXXH					
	Data		F0H					
Autoselect Manufacturer ID (1,2)	Add	4	555H	2AAH	DA/555H	DA/X00H		
	Data		AAH	55H	90H	ECH		
Autoselect Device Code (1,2,3)	Addr	4	555H	2AAH	DA/555H	DA/X01H	DA/X0EH	DA/X0FH
	Data		AAH	55H	90H	257EH	2500H	2501H
Autoselect BlockProtectVerify (1,2)	Addr	4	555H	2AAH	DA/555H	BA / X02H		
	Data		AAH	55H	90H	(See Table 7)		
Autoselect OTP Factory Protect	Addr	4	555H	2AAH	DA/555H	X03H		
	Data		AAH	55H	90H	(See Note 10)		
Program	Addr	4	555H	2AAH	555H	PA		
	Data		AAH	55H	A0H	PD		
Unlock Bypass	Addr	3	555H	2AAH	555H			
	Data		AAH	55H	20H			
Unlock Bypass Program	Addr	2	XXXH	PA				
	Data		A0H	PD				
Unlock Bypass Block Erase	Addr	2	XXXH	BA				
	Data		80H	30H				
Unlock Bypass Chip Erase	Addr	2	XXXH	XXXH				
	Data		80H	10H				
Unlock Bypass Reset	Addr	2	XXXH	XXXH				
	Data		90H	00H				
Unlock Bypass CFI	Addr	1	XXH					
	Data		98H					
Chip Erase	Addr	6	555H	2AAH	555H	555H	2AAH	555H
	Data		AAH	55H	80H	AAH	55H	10H
Block Erase	Addr	6	555H	2AAH	555H	555H	2AAH	BA
	Data		AAH	55H	80H	AAH	55H	30H
Block Erase Suspend (4, 5)	Addr	1	DA					
	Data		B0H					
Block Erase Resume	Addr	1	DA					
	Data		30H					
Program Suspend (6,7)	Addr	1	DA					
	Data		B0H					
Program Resume	Addr	1	DA					
	Data		30H					
CFI Query (8)	Addr	1	55H					
	Data		98H					



**K8P1615UQB**

**FLASH MEMORY**

**Table 6. Command Sequences (Continued)**

Command Definitions		Cycle	1st Cycle	2nd Cycle	3rd Cycle	4th Cycle	5th Cycle	6th Cycle
Accelerated Program	Addr	2	XXH	PA				
	Data		A0H	PD				
Quadruple word Accelerated Program(9)	Addr	5	XXXH	PA1	PA2	PA3	PA4	
	Data		A5H	PD1	PD2	PD3	PD4	
Enter OTP Block Region	Addr	3	555H	2AAH	555H			
	Data		AAH	55H	88H			
Exit OTP Block Region	Addr	4	555H	2AAH	555H	XXX		
	Data		AAH	55H	90H	00H		
OTP Protection bit Program (11,12)	Addr	6	555H	2AAH	555H	OW	OW	OW
	Data		AAH	55H	60H	68H	48H	RD(0)
OTP Protection bit Status	Addr	5	555H	2AAH	555H	OW	OW	
	Data		AAH	55H	60H	48H	RD(0)	

- Notes :**
- RA : Read Address, PA : Program Address, RD : Read Data, PD : Program Data
  - DA : Bank Address (A17- A19), BA : Block Address (A12 - A19), ABP : Address of the block to be protected or unprotected, X = Don't care .
  - OW = Address (A7:A0) is (00011010), RD(0) = Read Data DQ0 for protection indicator bit ,RD(1) = Read Data DQ1 for PPB Lock status.
  - DQ8 - DQ15 are don't care in command sequence, except for RD and PD.
  - A11 - A19 are also don't care, except for the case of special notice.
1. To terminate the Autoselect Mode, it is necessary to write Reset command to the register.
  2. The 4th cycle data of Autoselect mode is output data.  
The 3rd and 4th cycle bank addresses of Autoselect mode must be same.
  3. Device ID must be read across cycles 4, 5 and 6.  
K8P2815U(xOEh = 2508h, xOFh = 2501h), K8P6415U(xOEh = 2506h, xOFh = 2501h), K8P3215U(xOEh = 2503h, xOFh = 2501h)  
K8P1615U(xOEh = 2500h, xOFh = 2501h)
  4. The Read / Program operations at non-erasing blocks and the autoselect mode are allowed in the Erase Suspend mode.
  5. The Erase Suspend command is applicable only to the Block Erase operation.
  6. The Read Operation is allowed in the Program Suspend mode.
  7. The Program Suspend command is applicable to Program and Erase Suspend - Program operation.
  8. Command is valid when the device is in read mode or Autoselect mode.
  9. Quadruple word accelerated program is invoked only at Vpp=Vid, Vpp setup is required prior to this command sequence.  
PA1,PA2,PA3,PA4 have the same A19~A2 address
  10. The data is DQ6=1 for customer locked and DQ7=1 for factory locked.
  11. Reset command returns device to reading array.
  12. Cycle 4 programs the addressed locking bit. Cycle 5 and 6 validate bit has been fully programmed when DQ0=1. If DQ0=0 in cycle 6, program command must be issued and verified again.

**Table 7. K8P1615UQB Autoselect Codes, (High Voltage Method)**

Description		CE	OE	WE	A19 to A12	A10	A9	A8	A7	A6	A5 to A4	A3	A2	A1	A0	DQ15 to DQ8	DQ7 to DQ0
Manufacturer ID		L	L	H	DA	X	V <sub>id</sub>	X	L	L	X	L	L	L	L	X	ECH
Device ID	Read Cycle 1											L	L	L	H	25H	7EH
	Read Cycle 2	L	L	H	DA	X	V <sub>id</sub>	X	L	L	L	H	H	H	L	25H	00H
	Read Cycle 3											H	H	H	H	25H	01H
Block Protection Verification		L	L	H	BA	X	V <sub>id</sub>	X	L	L	L	L	L	H	L	X	01H(Protected) 00H (Unprotected)
OTP Indicator Bit (DQ7, DQ6)		L	L	H	DA	X	V <sub>id</sub>	X	X	L	L	L	L	H	H	X	DQ7=1(Factory locked) DQ6=1(Customer locked)
Master locking bit Indicator Bit		L	L	H	BA	X	V <sub>id</sub>	X	L	L	L	L	H	H	H	X	01H(Protected) 00H (Unprotected)

- Notes :** 1. L=Logic Low=V<sub>IL</sub>, H=Logic High=V<sub>IH</sub>, DA= Bank Address, BA=Block Address, X=Don't care.

DEVICE OPERATION

Read Mode

The K8P1615UQB is controlled by Chip Enable ( $\overline{CE}$ ), Output Enable ( $\overline{OE}$ ) and Write Enable ( $\overline{WE}$ ). When  $\overline{CE}$  and  $\overline{OE}$  are low and  $\overline{WE}$  is high, the data stored at the specified address location, will be the output of the device. The outputs are in high impedance state whenever  $\overline{CE}$  or  $\overline{OE}$  is high. The K8P1615UQB is available for Page mode. Page mode provides fast access time for high performance system.

Standby Mode

The K8P1615UQB features Stand-by Mode to reduce power consumption. This mode puts the device on hold when the device is deselected by making  $\overline{CE}$  high ( $\overline{CE} = V_{IH}$ ). Refer to the DC characteristics for more details on stand-by modes.

Output Disable

The device outputs are disabled when  $\overline{OE}$  is High ( $\overline{OE} = V_{IH}$ ). The output pins are in high impedance state.

Automatic Sleep Mode

The K8P1615UQB features Automatic Sleep Mode to minimize the device power consumption. When addresses remain steady for  $t_{AA}+30ns$ , the device automatically activates the Automatic Sleep Mode. In the sleep mode, output data is latched and always available to the system. When addresses are changed, the device provides new data without wait time.

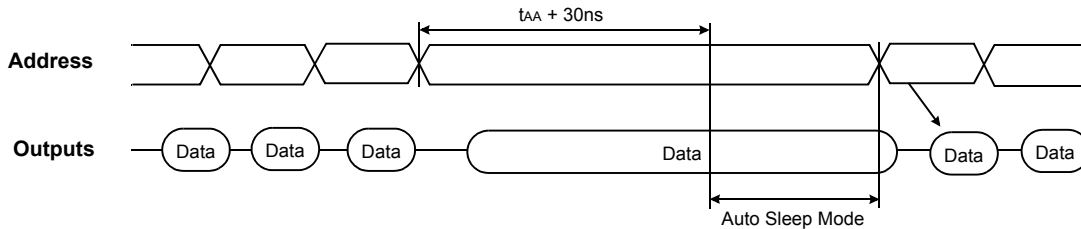
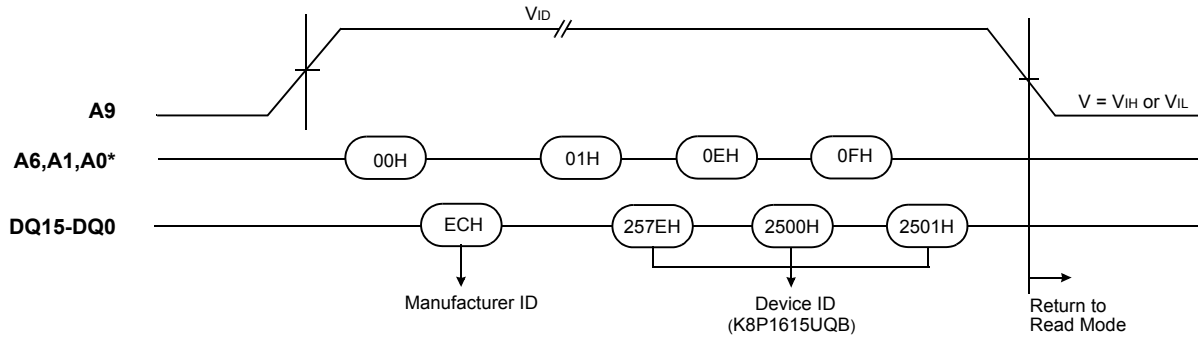


Figure 1. Auto Sleep Mode Operation

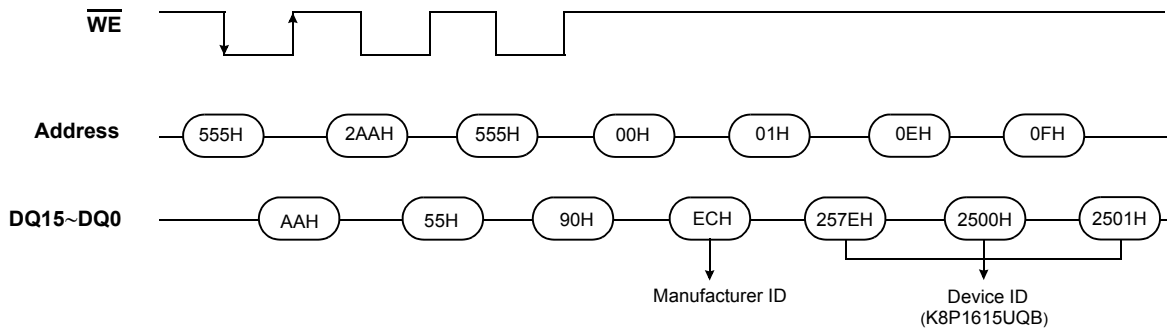
Autoselect Mode

The K8P1615UQB offers the Autoselect Mode to identify manufacturer, device type and block protection verification by reading a binary code. The Autoselect Mode allows programming equipment to automatically match the device to be programmed with its corresponding programming algorithm. In addition, this mode allows the verification of the status of write protected blocks. This mode is used by two method. The one is high voltage method to be required  $V_{ID}$  (8.5V - 9.5V) on address pin A9. When A9 is held at  $V_{ID}$  and the bank address or block address is asserted, the device outputs the valid data via DQ pins(see Table 7 and Figure 2). The rest of addresses except A0, A1 and A6 are don't care. The other is autoselect command method that the autoselect code is accessible by the commamd sequence without  $V_{ID}$ . The manufacturer, device code and block protection verification can be read via the command register. The Command Sequence is shown in Table 7 and Figure 3. The autoselect operation of block protection verification is initiated by first writing two unlock cycle. The third cycle must contain the bank address and autoselect command (90H). If Block address while (A6, A1, A0) = (0,1,0) is finally asserted on the address pin, it will produce a logical "1" at the device output DQ0 to indicate a write protected block or a logical "0" at the device output DQ0 to indicate a write unprotected block. To terminate the autoselect operation, write Reset command (F0H) into the command register.



**Note :** The addresses other than A0 , A1 and A6 are Don't care. Please refer to Table 7 for device code.

**Figure 2. Autoselect Operation ( by High Voltage Method )**



**Note :** The 3rd Cycle and 4th Cycle address must include the same bank address. Please refer to Table 7 for device code.

**Figure 3. Autoselect Operation ( by Command Sequence Method )**

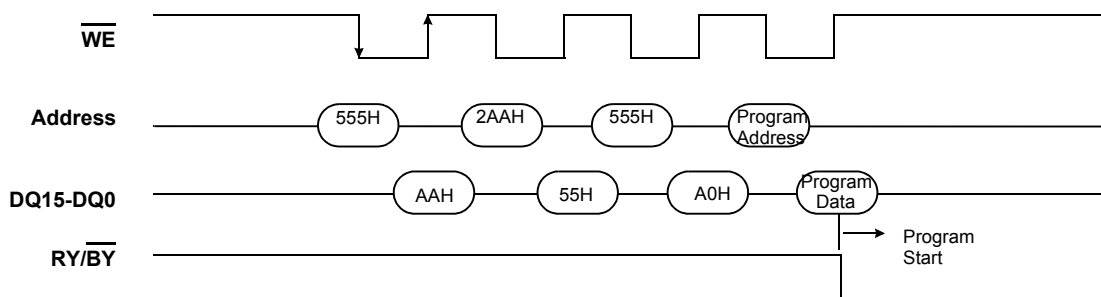
**Write (Program/Erase) Mode**

The K8P1615UQB executes its program/erase operations by writing commands into the command register. In order to write the commands to the register, CE and WE must be low and OE must be high. Addresses are latched on the falling edge of CE or WE (whichever occurs last) and the data are latched on the rising edge of CE or WE (whichever occurs first). The device uses standard microprocessor write timing.

**Program**

The K8P1615UQB can be programmed in units of a word. Programming is writing 0's into the memory array by executing the Internal Program Routine. In order to perform the Internal Program Routine, a four-cycle command sequence is necessary. The first two cycles are unlock cycles. The third cycle is assigned for the program setup command. In the last cycle, the address of the memory location and the data to be programmed at that location are written. The device automatically generates adequate program pulses and verifies the programmed cell margin by the Internal Program Routine. During the execution of the Routine, the system is not required to provide further controls or timings.

During the Internal Program Routine, commands written to the device will be ignored. Note that a hardware reset during a program operation will cause data corruption at the corresponding location.



**Figure 4. Program Command Sequence**

## K8P1615UQB

## FLASH MEMORY

In across block boundaries and any sequence programming is allowed. A bit cannot be programmed from '0' back to '1'. If attempting to do, it may cause that bank to set DQ5 = 1, or cause the DQ7 and DQ6 status bits to indicate the operation was successful. However, a succeeding read will show that the data is still '0'. Only erase operations can convert a '0' to a '1'.

### Unlock Bypass

The K8P1615UQB provides the unlock bypass mode to save its operation time. This mode is possible for program, block erase and chip erase operation. There are two methods to enter the unlock bypass mode. The mode is invoked by the unlock bypass command sequence. Unlike the standard program/erase command sequence that contains four to six bus cycles, the unlock bypass program/erase command sequence comprises only two bus cycles. The unlock bypass mode is engaged by issuing the unlock bypass command sequence which is comprised of three bus cycles. Writing first two unlock cycles is followed by a third cycle containing the unlock bypass command (20H). Once the device is in the unlock bypass mode, the unlock bypass program/erase command sequence is necessary. The unlock bypass program command sequence is comprised of only two bus cycles; writing the unlock bypass program command (A0H) is followed by the program address and data. This command sequence is the only valid one for programming the device in the unlock bypass mode. Also, The unlock bypass erase command sequence is comprised of two bus cycles; writing the unlock bypass block erase command(80H-30H) or writing the unlock bypass chip erase command(80H-10H). This command sequences are the only valid ones for erasing the device in the unlock bypass mode. The unlock bypass reset command sequence is the only valid command sequence to exit the unlock bypass mode. The unlock bypass reset command sequence consists of two bus cycles. The first cycle must contain the data (90H). The second cycle contains only the data (00H). Then, the device returns to the read mode.

### Chip Erase

To erase a chip is to write 1's into the entire memory array by executing the Internal Erase Routine. The Chip Erase requires six bus cycles to write the command sequence. The erase set-up command is written after first two "unlock" cycles. Then, there are two more write cycles prior to writing the chip erase command. The Internal Erase Routine automatically pre-programs and verifies the entire memory for an all zero data pattern prior to erasing. The automatic erase begins on the rising edge of the last WE or CE pulse in the command sequence and terminates when DQ7 is "1". After that the device returns to the read mode.

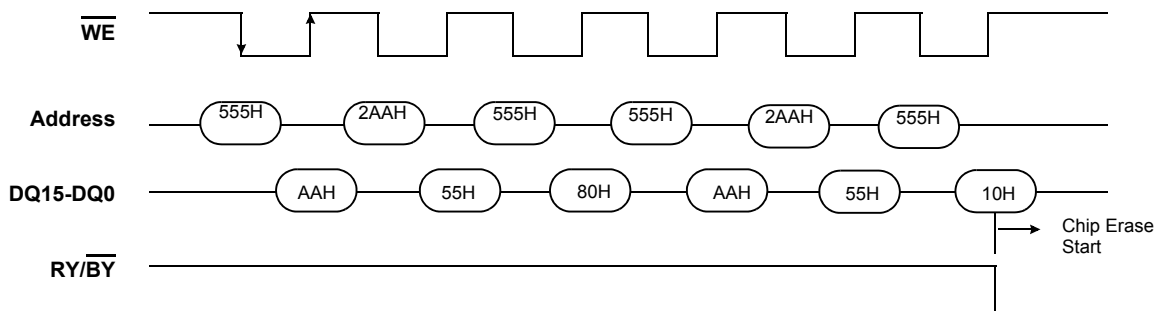


Figure 5. Chip Erase Command Sequence

### Block Erase

To erase a block is to write 1's into the desired memory block by executing the Internal Erase Routine. The Block Erase requires six bus cycles to write the command sequence shown in Table 6. After the first two "unlock" cycles, the erase setup command (80H) is written at the third cycle. Then there are two more "unlock" cycles followed by the Block Erase command. The Internal Erase Routine automatically pre-programs and verifies the entire memory prior to erasing it. The block address is latched on the falling edge of  $\overline{WE}$  or  $\overline{CE}$ , while the Block Erase command is latched on the rising edge of  $\overline{WE}$  or  $\overline{CE}$ .

Multiple blocks can be erased sequentially by writing the six bus-cycle operation in Figure 6. Upon completion of the last cycle for the Block Erase, additional block address and the Block Erase command (30H) can be written to perform the Multi-Block Erase. An 50us (typical) "time window" is required between the Block Erase command writes. The Block Erase command must be written within the 50us "time window", otherwise the Block Erase command will be ignored. The 50us "time window" is reset when the falling edge of the  $\overline{WE}$  occurs within the 50us of "time window" to latch the Block Erase command. During the 50us of "time window", any command other than the Block Erase or the Erase Suspend command written to the device will reset the device to read mode. After the 50 us of "time window", the Block Erase command will initiate the Internal Erase Routine to erase the selected blocks. Any Block Erase address and command following the exceeded "time window" may or may not be accepted. No other commands will be recognized except the Erase Suspend command.

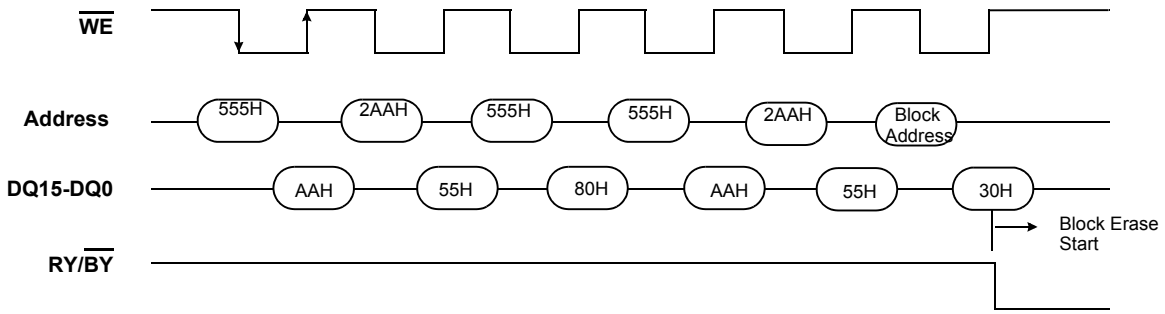


Figure 6. Block Erase Command Sequence

### Erase Suspend / Resume

The Erase Suspend command interrupts the Block Erase to read or program data in a block that is not being erased. The Erase Suspend command is only valid during the Block Erase operation including the time window of 50us. The Erase Suspend command is not valid while the Chip Erase or the Internal Program Routine sequence is running. When the Erase Suspend command is written during a Block Erase operation, the device requires a maximum of 20us to suspend the erase operation. But, when the Erase Suspend command is written during the block erase time window (50us), the device immediately terminates the block erase time window and suspends the erase operation. After the erase operation has been suspended, the device is available for reading or programming data in a block that is not being erased. The system may also write the autoselect command sequence when the device is in the Erase Suspend mode. When the Erase Resume command is executed, the Block Erase operation will resume. When the Erase Suspend or Erase Resume command is executed, the addresses are in Don't Care state.

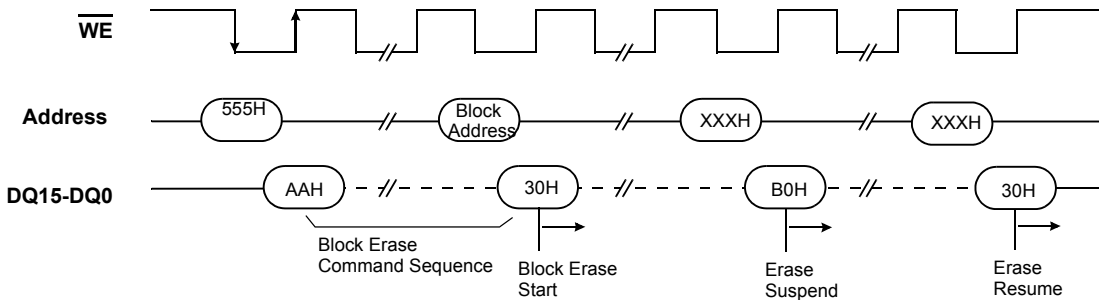


Figure 7. Erase Suspend/Resume Command Sequence

### Program Suspend / Resume

The Program Suspend command interrupts the Program operation. Also the Program Suspend command interrupts the Program operation during Erase Suspend Mode. The Read operation is available only during Program Suspend. When the Program Suspend command is written during a Program operation, the device requires a maximum of 10us to suspend the Program operation. The system may also write the autoselect command sequence when the device is in the Program Suspend mode. When the Program Resume command is executed, the Program operation will resume. When the Program Suspend or Program Resume command is executed, the addresses are in Don't Care state.

### Read While Write

The K8P1615UQB provides multi-bank memory architecture that divides the memory array into four banks. The device is capable of reading data from one bank and writing data to the other bank simultaneously. This is so called the Read While Write operation with multi-bank architecture; this feature provides the capability of executing the read operation during Program/Erase or Erase-Suspend-Program operation. The Read While Write operation is prohibited during the chip erase operation. It is also allowed during erase operation when either single block or multiple blocks from same bank are loaded to be erased. It means that the Read While Write operation is prohibited when blocks from one Bank and another blocks from the other Bank are loaded all together for the multi-block erase operation.

### Write Protect ( $\overline{WP}$ )

The  $\overline{WP/ACC}$  pin has two useful functions. The one is that certain boot block is protected by the hardware method not to use  $V_{IL}$ . The other is that program operation is accelerated to reduce the program time (Refer to Accelerated program Operation Paragraph). When the  $\overline{WP/ACC}$  pin is asserted at  $V_{IL}$ , the device can not perform program and erase operation in the two "outermost" 4Kword boot blocks on both ends of the flash array independently of whether those blocks were protected or unprotected using the method described in "Block protection/Unprotection". ( BA45 and BA44, BA0 and BA1)

The write protected blocks can only be read. This is useful method to preserve an important program data.

When the  $\overline{WP/ACC}$  pin is asserted at  $V_{IH}$ , the device reverts to whether the two outermost 4Kword boot blocks were last set to be protected or unprotected. That is, block protection or unprotection for these two blocks depends on whether they were last protected or unprotected using the method described in "Block protection/unprotection".

Recommend that the  $\overline{WP/ACC}$  pin must not be in the state of floating or unconnected, otherwise the device may be led to malfunction.

### Software Reset

The reset command provides that the bank is reseted to read mode or erase-suspend-read mode. The addresses are in Don't Care state. The reset command is valid between the sequence cycles in an erase command sequence before erasing begins, or in a program command sequence before programming begins. This resets the bank in which was operating to read mode. if the device is erasing or programming, the reset command is invalid until the operation is completed. Also, the reset command is valid between the sequence cycles in an autoselect command sequence. In the autoselect mode, the reset command returns the bank to read mode. If a bank entered the autoselect mode in the Erase Suspend mode, the reset command returns the bank to erase-suspend-read mode. If DQ5 is high on erase or program operation, the reset command return the bank to read mode or erase-suspend-read mode if the bank was in the Erase Suspend state.

### Hardware Reset

The K8P1615UQB offers a reset feature by driving the  $\overline{RESET}$  pin to  $V_{IL}$ . The  $\overline{RESET}$  pin must be kept low ( $V_{IL}$ ) for at least 500ns. When the  $\overline{RESET}$  pin is driven low, any operation in progress will be terminated and the internal state machine will be reset to the standby mode after 20us. If a hardware reset occurs during a program operation, the data at that particular location will be lost. Once the  $\overline{RESET}$  pin is taken high, the device requires 200ns of wake-up time until outputs are valid for read access. Also, note that all the data output pins are tri-stated for the duration of the  $\overline{RESET}$  pulse.

The  $\overline{RESET}$  pin may be tied to the system reset pin. If a system reset occurs during the Internal Program and Erase Routine, the device will be automatically reset to the read mode ; this will enable the systems microprocessor to read the boot-up firmware from the Flash memory.

### Power-up Protection

To avoid initiation of a write cycle during Vcc Power-up,  $\overline{\text{RESET}}$  low must be asserted during power-up. After  $\overline{\text{RESET}}$  goes high, the device is reset to the read mode.

### Low Vcc Write Inhibit

To avoid initiation of a write cycle during Vcc power-up and power-down, a write cycle is locked out for Vcc less than 2.3V. If Vcc < VLKO (Lock-Out Voltage), the command register and all internal program/erase circuits are disabled. Under this condition the device will reset itself to the read mode. Subsequent writes will be ignored until the Vcc level is greater than VLKO. It is the user's responsibility to ensure that the control pins are logically correct to prevent unintentional writes when Vcc is above 2.3V.

### Write Pulse Glitch Protection

Noise pulses of less than 5ns(typical) on  $\overline{\text{CE}}$ ,  $\overline{\text{OE}}$ , or  $\overline{\text{WE}}$  will not initiate a write cycle.

### Logical Inhibit

Writing is inhibited under any one of the following conditions :  $\overline{\text{OE}} = \text{VIL}$ ,  $\overline{\text{CE}} = \text{VIH}$  or  $\overline{\text{WE}} = \text{VIH}$ . To initiate a write,  $\overline{\text{CE}}$  and  $\overline{\text{WE}}$  must be "0", while  $\overline{\text{OE}}$  is "1".

### Common Flash Memory Interface

Common Flash Memory Interface is contrived to increase the compatibility of host system software. It provides the specific information of the device, such as memory size, word configuration, and electrical features. Once this information has been obtained, the system software will know which command sets to use to enable flash writes, block erases, and control the flash component. When the system writes the CFI command(98H) to address 55H in word mode, the device enters the CFI mode. And then if the system writes the address shown in Table 8, the system can read the CFI data. Query data are always presented on the lowest-order data outputs(DQ0-7) only. In word(x16) mode, the upper data outputs(DQ8-15) is 00h. To terminate this operation, the system must write the reset command.

### OTP Block Region

The OTP Block feature provides a 256-word Flash memory region that enables permanent part identification through an Electronic Serial Number (ESN). The OTP Block is customer lockable and shipped with itself unlocked, allowing customers to utilize the that block in any manner they choose. Indicator bits DQ6 and DQ7 are used to indicate the factory-locked and customer locked status of the part. The data is DQ6 = "1" for customer locked and DQ7 = "1" for factory locked.

The system accesses the OTP Block through a command sequence (see "Enter OTP Block / Exit OTP Block Command sequence" at Table 6). After the system has written the "Enter OTP Block" Command sequence, it may read the OTP Block by using the addresses (000000h~0000FFh) normally and may check the Protection Verify Bit (DQ7,DQ6) by using the "Autoselect Block Protection Verify" Command sequence with OTP Block address. This mode of operation continues until the system issues the "Exit OTP Block" Command sequence, a hardware reset or until power is removed from the device. On power-up, or following a hardware reset, the device reverts to sending commands to main blocks. Note that the Accelerated function and unlock bypass modes are not available when the OTP Block is enabled.

### Customer Lockable

In a Customer lockable device, The OTP Block is one-time programmable and can be locked only once. Note that the Accelerated programming and Unlock bypass functions are not available when programming the OTP Block. Locking operation to the OTP Block is started by writing the "Enter OTP Block" Command sequence, and it can be permanently locked to "1" by issuing the OTP Protection bit program Command sequence. Once the OTP block is locked and verified, the system must write the Exit OTP block command to return to reading and writing the remainder of the array.

### OTP Protection Bits

OTP protection bits prevent programming of the OTP block memory area. Once set, the OTP area are non-modifiable.

- The OTP Block Lock operation must be used with caution since, once locked, there is no procedure available for unlocking and none of the bits in the OTP Block space can be modified in any way.
- Suspend and resume operation are not supported during OTP protect, nor is OTP protect supported during any suspend operation.



### **High Voltage Block Protection**

Block protection and unprotection may also be implemented using programming equipment. The procedure requires high voltage (V<sub>id</sub>) to be placed on the RESET# pin. Refer to Figure 8 for details on this procedure. Note that for block unprotect, all unprotected blocks must first be protected prior to the first sector write cycle.

### **Accelerated Program Operation**

Accelerated program operation is one of two functions provided by the  $\overline{WP/ACC}$  pin. When the  $\overline{WP/ACC}$  pin is asserted as V<sub>HH</sub>, the device automatically enters the Unlock Bypass mode, temporarily unprotecting any protected blocks. The system would use a two-cycle program command sequence as required by the Unlock Bypass mode. Removing V<sub>HH</sub> from the  $\overline{WP/ACC}$  pin returns the device to normal operation.

**Recommend that the  $\overline{WP/ACC}$  pin must not be asserted at V<sub>HH</sub> except on accelerated program operation, or the device may be damaged. In addition, the  $\overline{WP/ACC}$  pin must not be in the state of floating or unconnected, otherwise the device may be led to malfunction.**

### **Single word accelerated program operation**

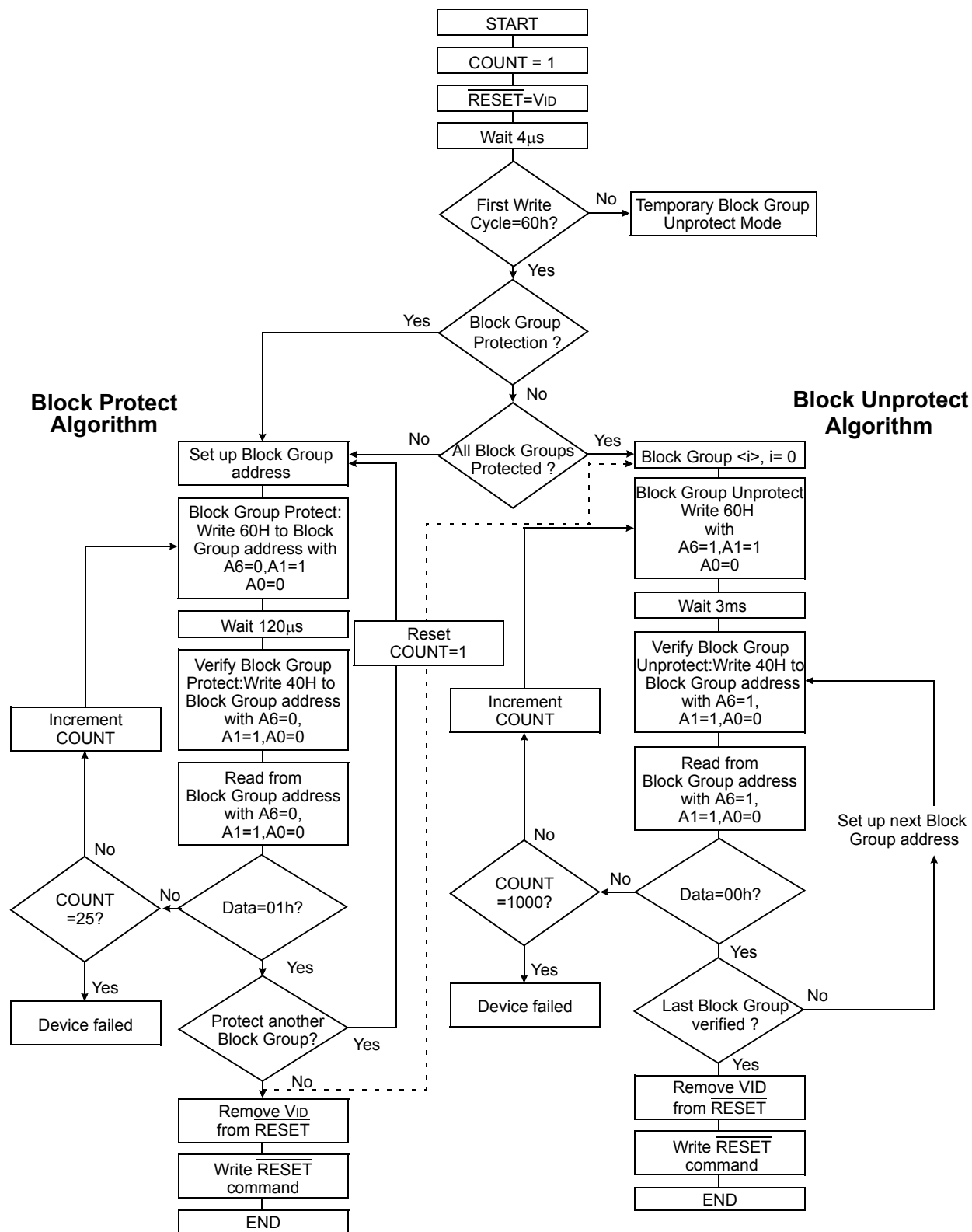
The system would use two-cycle program sequence (One-cycle (XXX - A0H) is for single word program command, and Next one-cycle (PA - PD) is for program address and data ).

### **Quadruple word accelerated program operation**

As well as Single word accelerated program, the system would use five-cycle program sequence (One-cycle (XXX - A5H) is for quadruple word program command, and four cycles are for program address and data).

- Only four words programming is possible
- Each program address must have the same A19~A2 address
- The device automatically generates adequate program pulses and ignores other command after program command
- Program/Erase cycling must be limited below 100cycles for optimum performance.
- Read while Write mode is not guaranteed

**Requirements : Ambient temperature : T<sub>A</sub>=30°C±10°C**



Note : All blocks must be protected before unprotect operation is executing.

Figure 8. Block Group Protection & Unprotection Algorithms

Table 8. Block Protection Schemes

DYB	PPB	PPB Lock	Block State
0	0	0	Unprotected-PPB and DYB are changeable
0	0	1	Unprotected-PPB not changeable and DYB are changeable
0	1	0	Protected-PPB and DYB are changeable
1	0	0	
1	1	0	
0	1	1	Protected-PPB not changeable, DYB is changeable
1	0	1	
1	1	1	

**Block Protection**

The K8P1615UQB features several levels of block protection, which can disable both the program and erase operations in certain blocks or block groups:

**Persistent Block Protection**

A command block protection method that replaces the old 12 V controlled protection method.

**Password Block Protection**

A highly sophisticated protection method that requires a password before changes to certain blocks or block groups are permitted

**Selecting a Block Protection Mode**

All parts default to operate in the Persistent Block Protection mode. The customer must then choose if the Persistent or Password Protection method is most desirable. There are two one-time programmable non-volatile bits that define which block protection-method will be used. If the Persistent Block Protection method is desired, programming the Persistent Block Protection Mode Locking Bit permanently sets the device to the Persistent Block Protection mode. If the Password Block Protection method is desired, programming the Password Mode Locking Bit permanently sets the device to the Password Block Protection mode.

It is not possible to switch between the two protection modes once a locking bit has been set. One of the two modes must be selected when the device is first programmed. This prevents a program or virus from later setting the Password Mode Locking Bit, which would cause an unexpected shift from the default Persistent Block Protection Mode into the Password Protection Mode.

The device is shipped with all blocks unprotected. Optional Samsung programming services enable programming and protecting blocks at the factory prior to shipping the device. Contact your local sales office for details.

It is possible to determine whether a block is protected or unprotected. See Autoselect Mode for details.

**Persistent Block Protection**

The Persistent Block Protection method replaces the 12 V controlled protection method in previous flash devices. This new method provides three different block protection states:

- Persistently Locked - The block is protected and cannot be changed.
- Dynamically Locked - The block is protected and can be changed by a simple command.
- Unlocked - The block is unprotected and can be changed by a simple command.

To achieve these states, three types of "bits" are used:

- Persistent Protection Bit
- Persistent Protection Bit Lock
- Persistent Block Protection Mode Locking Bit

**Persistent Protection Bit (PPB)**

A single Persistent (non-volatile) Protection Bit is assigned to a maximum four blocks (see the block address tables for specific block protection groupings). All 4 Kword boot-block sectors have individual block Persistent Protection Bits(PPBs) for greater flexibility. Each PPB is individually modifiable through the PPB Write Command.

The device erases all PPBs in parallel. If any PPB requires erasure, the device must be instructed to preprogram all of the block PPBs prior to PPB erasure. Otherwise, a previously erased block PPBs can potentially be over-erased. The flash device does not have a built-in means of preventing block PPBs over-erasure.

**Persistent Protection Bit Lock (PPB Lock)**

The Persistent Protection Bit Lock (PPB Lock) is a global volatile bit. When set to "1", the PPBs cannot be changed. When cleared "0", the PPBs are changeable. There is only one PPB Lock bit per device. The PPB Lock is cleared after power-up or hardware reset. There is no command sequence to unlock the PPB Lock.

**Dynamic Protection Bit (DYB)**

A volatile protection bit is assigned for each block. After power-up or hardware reset, the contents of all DYBs is "0". Each DYB is individually modifiable through the DYB Write Command.

When the parts are first shipped, the PPBs are cleared, the DYBs are cleared, and PPB Lock is defaulted to power up in the cleared state - meaning the PPBs are changeable. When the device is first powered on the DYBs power up cleared (blocks not protected). The Protection State for each sector is determined by the logical OR of the PPB and the DYB related to that block. For the blocks that have the PPBs cleared, the DYBs control whether or not the block is protected or unprotected.

By issuing the DYB Write command sequences, the DYBs will be set or cleared, thus placing each block in the protected or unprotected state. These are the so-called Dynamic Locked or Unlocked states. They are called dynamic states because it is very easy to switch back and forth between the protected and unprotected conditions. This allows software to easily protect blocks against inadvertent changes yet does not prevent the easy removal of protection when changes are needed. The DYBs maybe set or cleared as often as needed.

The PPBs allow for a more static, and difficult to change, level of protection. The PPBs retain their state across power cycles because they are non-volatile. Individual PPBs are set with a command but must all be cleared as a group through a complex sequence of program and erasing commands. The PPBs are also limited to 100 erase cycles.

The PPB Lock bit adds an additional level of protection. Once all PPBs are programmed to the desired settings, the PPB Lock may be set to "1". Setting the PPB Lock disables all program and erase commands to the non-volatile PPBs. In effect, the PPB Lock Bit locks the PPBs into their current state. The only way to clear the PPB Lock is to go through a power cycle. System boot code can determine if any changes to the PPB are needed; for example, to allow new system code to be downloaded. If no changes are needed then the boot code can set the PPB Lock to disable any further changes to the PPBs during system operation.

The WP#/ACC write protect pin adds a final level of hardware protection to blocks BA44 and BA45, BA0 and BA1. When this pin is low it is not possible to change the contents of these blocks. These blocks generally hold system boot code. The WP#/ACC pin can prevent any changes to the boot code that could override the choices made while setting up block protection during system initialization.

For customers who are concerned about malicious viruses there is another level of security - the persistently locked state. To persistently protect a given block or block group, the PPBs associated with that block need to be set to "1". Once all PPBs are programmed to the desired settings, the PPB Lock should be set to "1". Setting the PPB Lock automatically disables all program and erase commands to the Non-Volatile PPBs. In effect, the PPB Lock "freezes" the PPBs into their current state. The only way to clear the PPB Lock is to go through a power cycle.

It is possible to have blocks that have been persistently locked, and blocks that are left in the dynamic state. The blocks in the dynamic state are all unprotected. If there is a need to protect some of them, a simple DYB Write command sequence is all that is necessary. The DYB write command for the dynamic blocks switch the DYBs to signify protected and unprotected, respectively. If there is a need to change the status of the persistently locked blocks, a few more steps are required. First, the PPB Lock bit must be disabled by either putting the device through a power-cycle, or hardware reset. The PPBs can then be changed to reflect the desired settings. Setting the PPB lock bit once again will lock the PPBs, and the device operates normally again.

The best protection is achieved by executing the PPB lock bit set command early in the boot code, and protect the boot code by holding WP#/ACC = VIL.

Table 8 contains all possible combinations of the DYB, PPB, and PPB lock relating to the status of the block.

In summary, if the PPB is set, and the PPB lock is set, the block is protected and the protection can not be removed until the next power cycle clears the PPB lock. If the PPB is cleared, the block can be dynamically locked or unlocked. The DYB then controls whether or not the block is protected or unprotected.

If the user attempts to program or erase a protected block, the device ignores the command and returns to read mode. A program command to a protected block enables status polling for approximately 1us before the device returns to read mode without having modified the contents of the protected block. An erase command to a protected block enables status polling for approximately 50us after which the device returns to read mode without having erased the protected block.

The programming of the DYB, PPB, and PPB lock for a given block can be verified by writing a DYB/PPB/PPB lock verify command to the device.

#### **Persistent Block Protection Mode Locking Bit**

Like the password mode locking bit, a Persistent Block Protection mode locking bit exists to guarantee that the device remain in software block protection. Once set, the Persistent Block Protection locking bit prevents programming of the password protection mode locking bit. This guarantees that a hacker could not place the device in password protection mode.

### **Password Protection Mode**

The Password Block Protection Mode method allows an even higher level of security than the Persistent Block Protection Mode. There are two main differences between the Persistent Block Protection and the Password Block Protection Mode:

When the device is first powered on, or comes out of a reset cycle, the PPB Lock bit set to the locked state, rather than cleared to the unlocked state.

The only means to clear the PPB Lock bit is by writing a unique 64-bit Password to the device.

The Password Block Protection method is otherwise identical to the Persistent Block Protection method.

A 64-bit password is the only additional tool utilized in this method.

Once the Password Mode Locking Bit is set, the password is permanently set with no means to read, program, or erase it. The password is used to clear the PPB Lock bit. The Password Unlock command must be written to the flash, along with a password. The flash device internally compares the given password with the pre-programmed password. If they match, the PPB Lock bit is cleared, and the PPBs can be altered. If they do not match, the flash device does nothing. There is a built-in 2us delay for each "password check." This delay is intended to thwart any efforts to run a program that tries all possible combinations in order to crack the password.

#### **Password and Password Mode Locking Bit**

In order to select the Password block protection scheme, the customer must first program the password. The password may be correlated to the unique Electronic Serial Number (ESN) of the particular flash device. Each ESN is different for every flash device; therefore each password should be different for every flash device. While programming in the password region, the customer may perform Password Verify operations.

Once the desired password is programmed in, the customer must then set the Password Mode Locking Bit. This operation achieves two objectives:

Permanently sets the device to operate using the Password Protection Mode. It is not possible to reverse this function.

Disables all further commands to the password region. All program, and read operations are ignored.

Both of these objectives are important, and if not carefully considered, may lead to unrecoverable errors. The user must be sure that the Password Protection method is desired when setting the Password Mode Locking Bit. More importantly, the user must be sure that the password is correct when the Password Mode Locking Bit is set. Due to the fact that read operations are disabled, there is no means to verify what the password is afterwards. If the password is lost after setting the Password Mode Locking Bit, there will be no way to clear the PPB Lock bit.

The Password Mode Locking Bit, once set, prevents reading the 64-bit password on the DQ bus and further password programming. The Password Mode Locking Bit is not erasable. Once Password Mode Locking Bit is programmed, the Persistent Block Protection Locking Bit is disabled from programming, guaranteeing that no changes to the protection scheme are allowed.

#### **64-bit Password**

The 64-bit Password is located in its own memory space and is accessible through the use of the Password Program and Verify commands (see "Password Verify Command"). The password function works in conjunction with the Password Mode Locking Bit, which when set, prevents the Password Verify command from reading the contents of the password on the pins of the device.

#### **Write Protect (WP#)**

The Write Protect feature provides a hardware method of protecting the upper two and lower two blocks without using VID. This function is provided by the WP# pin and overrides the previously discussed "High Voltage Block Protection" section method.

If the system asserts VIL on the WP#/ACC pin, the device disables program and erase functions in the two outermost 4 Kword blocks on both ends of the flash array independent of whether it was previously protected or unprotected.

If the system asserts VIH on the WP#/ACC pin, the device reverts the upper two and lower two blocks to whether they were last set to be protected or unprotected. That is, block protection or unprotection for these sectors depends on whether they were last protected or unprotected using the method described in the "High Voltage Block Protection" section.

**Persistent Protection Bit Lock**

The Persistent Protection Bit (PPB) Lock is a volatile bit that reflects the state of the Password Mode Locking Bit after power-up reset. If the Password Mode Lock Bit is also set after a hardware reset (RESET# asserted) or a power-up reset, the ONLY means for clearing the PPB Lock Bit in Password Protection Mode is to issue the Password Unlock command. Successful execution of the Password Unlock command clears the PPB Lock Bit, allowing for block PPBs modifications. Asserting RESET#, taking the device through a power-on reset, or issuing the PPB Lock Bit Set command sets the PPB Lock Bit to a "1" when the Password Mode Lock Bit is not set.

If the Password Mode Locking Bit is not set, including Persistent Protection Mode, the PPB Lock Bit is cleared after power-up or hardware reset. The PPB Lock Bit is set by issuing the PPB Lock Bit Set command. Once set the only means for clearing the PPB Lock Bit is by issuing a hardware or power-up reset. The Password Unlock command is ignored in Persistent Protection Mode.

**Master locking bit set**

This Master locking bit can ensure that protected blocks be permanently unalterable.

Master locking bit is non-volatile bit. Master locking bit controls protection status of entire blocks.

The usage of the master locking bit command sequence is absolutely required to ensure full protection of data from future alterations. If master locking bit is set ("1"), entire blocks are permanently protected. They are not changed and altered by any future lock/unlock commands.

Anyone who uses this function needs much attention. Because there is no way to return to unlock status. Default status of master locking bit is unlock status("0").

If Master locking bit sets on unprotected block, the block still are remaining in status of unprotected block.

The unprotected block can be protected by protection command.

**K8P1615UQB**

**FLASH MEMORY**

**Table 9. K8P1615UQB Boot Block/Block Addresses for Protection / Unprotection**

Block	A19-A12	Block Size
BA0	00000000	4 Kwords
BA1	00000001	4 Kwords
BA2	00000010	4 Kwords
BA3	00000011	4 Kwords
BA4	00000100	4 Kwords
BA5	00000101	4 Kwords
BA6	00000110	4 Kwords
BA7	00000111	4 Kwords
BA8	00001XXX	32 Kwords
BA9	00010XXX	32 Kwords
BA10	00011XXX	32 Kwords
BA11-BA14	001XXXXX	128 (4x32) Kwords
BA15-BA18	010XXXXX	128 (4x32) Kwords
BA19-BA22	011XXXXX	128 (4x32) Kwords
BA23-BA26	100XXXXX	128 (4x32) Kwords
BA27-BA30	101XXXXX	128 (4x32) Kwords
BA31-BA34	110XXXXX	128 (4x32) Kwords
BA35	11100XXX	32 Kwords
BA36	11101XXX	32 Kwords
BA37	11110XXX	32 Kwords
BA38	11111000	4 Kwords
BA39	11111001	4 Kwords
BA40	11111010	4 Kwords
BA41	11111011	4 Kwords
BA42	11111100	4 Kwords
BA43	11111101	4 Kwords
BA44	11111110	4 Kwords
BA45	11111111	4 Kwords

**K8P1615UQB**

**FLASH MEMORY**

**Table 10. Block Protection Command Sequences**

Command Sequence		Cycle	1st Cycle	2nd Cycle	3rd Cycle	4th Cycle	5th Cycle	6th Cycle	7th Cycle
Password Program(1,2)	Addr	4	555H	2AAH	555H	XX[0-3]H			
	Data		AAH	55H	38H	PD[0-3]			
Password Verify(2,4,5)	Addr	4	555H	2AAH	555H	PWA[0-3]			
	Data		AAH	55H	C8H	PWD[0-3]			
Password Unlock(3,6,7)	Addr	7	555H	2AAH	555H	PWA[0]	PWA[1]	PWA[2]	PWA[3]
	Data		AAH	55H	28H	PWD[0]	PWD[1]	PWD[2]	PWD[3]
PPB Program(1,2,8)	Addr	6	555H	2AAH	555H	(BA)WP	(BA)WP	(BA)WP	
	Data		AAH	55H	60H	68H	48H	RD(0)	
Master locking bit Set	Addr	3	555H	2AAH	555H				
	Data		AAH	55H	F1H				
PPB Status	Addr	4	555H	2AAH	555H	(BA)WP			
	Data		AAH	55H	90H	RD(0)			
All PPB Erase(1,2,9,10)	Addr	6	555H	2AAH	555H	WP	(BA)	(BA)WP	
	Data		AAH	55H	60H	60H	40H	RD(0)	
PPB Lock Bit Set	Addr	3	555H	2AAH	555H				
	Data		AAH	55H	78H				
PPB Lock Bit Status(11)	Addr	4	555H	2AAH	555H	BA			
	Data		AAH	55H	58H	RD(1)			
DYB Write(3)	Addr	4	555H	2AAH	555H	BA			
	Data		AAH	55H	48H	X1H			
DYB Erase(3)	Addr	4	555H	2AAH	555H	BA			
	Data		AAH	55H	48H	X0H			
DYB Status(2)	Addr	4	555H	2AAH	(DA)555H	BA			
	Data		AAH	55H	58H	RD(0)			
PPMLB Program(1,2,8)	Addr	6	555H	2AAH	555H	PL	PL	PL	
	Data		AAH	55H	60H	68H	48H	RD(0)	
PPMLB Status(1)	Addr	5	555H	2AAH	555H	PL	PL		
	Data		AAH	55H	60H	48H	RD(0)		
SPMLB Program(1,2,8)	Addr	6	555H	2AAH	555H	BL	BL	BL	
	Data		AAH	55H	60H	68	48	RD(0)	
SPMLB Status(1)	Addr	5	555H	2AAH	555H	BL	BL		
	Data		AAH	55H	60H	48	RD(0)		

**Legend:**

DYB = Dynamic Protection Bit

OW = Address (A7:A0) is (00011010)

PD[3:0] = Password Data (1 of 4 portions)

PPB = Persistent Protection Bit

PWA = Password Address. A1:A0 selects portion of password.

PWD = Password Data being verified.

PL = Password Protection Mode Lock Address (A7:A0) is (00001010)

RD(0) = Read Data DQ0 for protection indicator bit.

RD(1) = Read Data DQ1 for PPB Lock status.

BA = Block Address where security command applies. Address bits Amax:A12 uniquely select any block.

BL = Persistent Protection Mode Lock Address (A7:A0) is (00010010)

WP = PPB Address (A7:A0) is (00000010)



X = Don't care

PPMLB = Password Protection Mode Locking Bit

SPMLB = Persistent Protection Mode Locking Bit

Notes:

- See the description of bus operations.
  - All values are in hexadecimal.
  - Shaded cells in table denote read cycles. All other cycles are write operations.
  - During unlock and command cycles, when lower address bits are 555 or 2AAh as shown in table, address bits higher than A11 (except where BA is required) and data bits higher than DQ7 are don't cares.
1. The reset command returns device to reading array.
  2. Cycle 4 programs the addressed locking bit. Cycles 5 and 6 validate bit has been fully programmed when DQ0 = 1. If DQ0 = 0 in cycle 6, program command must be issued and verified again.
  3. Data is latched on the rising edge of WE#.
  4. Entire command sequence must be entered for each portion of password.
  5. Command sequence returns FFh if PPMLB is set.
  6. The password is written over four consecutive cycles, at addresses 0-3.
  7. 2 $\mu$ s timeout is required between any two portions of password.
  8. 100 $\mu$ s timeout is required between cycles 4 and 5.
  9. 1.2 ms timeout is required between cycles 4 and 5.
  10. Cycle 4 erases all PPBs. Cycles 5 and 6 validate bits have been fully erased when DQ0 = 0. If DQ0 = 1 in cycle 6, erase command must be issued and verified again. Before issuing erase command, all PPBs should be programmed to prevent PPB overerasure.
  11. DQ1 = 1 if PPB locked, 0 if unlocked.

**K8P1615UQB**

**FLASH MEMORY**

**Table 11. Common Flash Memory Interface Code**

Description	Addresses (Word Mode)	Data
Query Unique ASCII string "QRY"	10H 11H 12H	0051H 0052H 0059H
Primary OEM Command Set	13H 14H	0002H 0000H
Address for Primary Extended Table	15H 16H	0040H 0000H
Alternate OEM Command Set (00h = none exists)	17H 18H	0000H 0000H
Address for Alternate OEM Extended Table (00h = none exists)	19H 1AH	0000H 0000H
Vcc Min. (write/erase) D7-D4: volt, D3-D0: 100 millivolt	1BH	0027H
Vcc Max. (write/erase) D7-D4: volt, D3-D0: 100 millivolt	1CH	0036H
Vpp Min. voltage(00H = no Vpp pin present)	1DH	0000H
Vpp Max. voltage(00H = no Vpp pin present)	1EH	0000H
Typical timeout per single word write 2 <sup>N</sup> us	1FH	0003H
Typical timeout for Min. size buffer write 2 <sup>N</sup> us(00H = not supported)	20H	0000H
Typical timeout per individual block erase 2 <sup>N</sup> ms	21H	0009H
Typical timeout for full chip erase 2 <sup>N</sup> ms(00H = not supported)	22H	0000H
Max. timeout for word write 2 <sup>N</sup> times typical	23H	0004H
Max. timeout for buffer write 2 <sup>N</sup> times typical	24H	0000H
Max. timeout per individual block erase 2 <sup>N</sup> times typical	25H	0004H
Max. timeout for full chip erase 2 <sup>N</sup> times typical(00H = not supported)	26H	0000H
Device Size = 2 <sup>N</sup> byte	27H	0015H
Flash Device Interface description	28H 29H	0001H 0000H
Max. number of byte in multi-byte write = 2 <sup>N</sup>	2AH 2BH	0000H 0000H
Number of Erase Block Regions within device	2CH	0003H
Erase Block Region 1 Information	2DH 2EH 2FH 30H	0007H 0000H 0020H 0000H
Erase Block Region 2 Information	31H 32H 33H 34H	001DH 0000H 0000H 0001H
Erase Block Region 3 Information	35H 36H 37H 38H	0007H 0000H 0020H 0000H
Erase Block Region 4 Information	39H 3AH 3BH 3CH	0000H 0000H 0000H 0000H

**K8P1615UQB****FLASH MEMORY****Table 11. Common Flash Memory Interface Code**

Description	Addresses (Word Mode)	Data
Query-unique ASCII string "PRI"	40H 41H 42H	0050H 0052H 0049H
Major version number, ASCII	43H	0030H
Minor version number, ASCII	44H	0030H
Address Sensitive Unlock(Bits 1-0) 0 = Required, 1= Not Required Silcon Revision Number(Bits 7-2)	45H	0000H
Erase Suspend 0 = Not Supported, 1 = To Read Only, 2 = To Read & Write	46H	0002H
Block Protect 00 = Not Supported, 01 = Supported	47H	0001H
Block Temporary Unprotect 00 = Not Supported, 01 = Supported	48H	0001H
Block Protect/Unprotect scheme, 00 = Not Supported, 01 = Supported	49H	0001H
Simultaneous Operation 00 = Not Supported, 01 = Supported	4AH	0001H
Burst Mode Type 00 = Not Supported, 01 = Supported	4BH	0000H
Page Mode Type 00 = Not Supported, 01 = 4 Word Page 02 = 8 Word Page	4CH	0002H
ACC(Acceleration) Supply Minimum 00 = Not Supported, D7 - D4 : Volt, D3 - D0 : 100mV	4DH	0085H
ACC(Acceleration) Supply Maximum 00 = Not Supported, D7 - D4 : Volt, D3 - D0 : 100mV	4EH	0095H
Top/Bottom Boot Block Flag 02H = Bottom Boot Device, 03H = Top Boot Device, 04H = Top and Bottom Device	4FH	0004H

**DEVICE STATUS FLAGS**

The K8P1615UQB has means to indicate its status of operation in the bank where a program or erase operation is in processes. Address must include bank address being executed internal routine operation. The status is indicated by raising the device status flag via corresponding DQ pins or the RY/ BY pin. The corresponding DQ pins are DQ7, DQ6, DQ5, DQ3 and DQ2. The statuses are as follows :

**Table 12. Hardware Sequence Flags**

	Status	DQ7	DQ6	DQ5	DQ3	DQ2	RY/BY	
In Progress	Programming	$\overline{DQ7}$	Toggle	0	0	1	0	
	Block Erase or Chip Erase	0	Toggle	0	1	Toggle	0	
	Erase Suspend Read	Erase Suspended Block	1	1	0	0	Toggle (Note 1)	1
	Erase Suspend Read	Non-Erase Suspended Block	Data	Data	Data	Data	Data	1
	Erase Suspend Program	Non-Erase Suspended Block	$\overline{DQ7}$	Toggle	0	0	1	0
	Program Suspend Read	Program Suspended Block	DQ7	1	0	0	Toggle (Note 1)	1
	Program Suspend Read	Non-Program Suspended Block	Data	Data	Data	Data	Data	1
Exceeded Time Limits	Programming	$\overline{DQ7}$	Toggle	1	0	No Toggle	0	
	Block Erase or Chip Erase	0	Toggle	1	1	(Note 2)	0	
	Erase Suspend Program	$\overline{DQ7}$	Toggle	1	0	No Toggle	0	

**Notes :**

1. DQ2 will toggle when the device performs successive read operations from the erase/program suspended block.
2. If DQ5 is High (exceeded timing limits), successive reads from a problem block will cause DQ2 to toggle.

**DQ7 : Data Polling**

When an attempt to read the device is made while executing the Internal Program, the complement of the data is written to DQ7 as an indication of the Routine in progress. When the Routine is completed an attempt to access to the device will produce the true data written to DQ7. When a user attempts to read the block being erased, DQ7 will be low. If the device is placed in the Erase/Program Suspend Mode, the status can be detected via the DQ7 pin. If the system tries to read an address which belongs to a block that is being erase suspended, DQ7 will be high. And, if the system tries to read an address which belongs to a block that is being program suspended, the output will be the true data of DQ7 itself. If a non-erase-suspended or non-program-suspended block address is read, the device will produce the true data to DQ7. If an attempt is made to program a protected block, DQ7 outputs complements the data for approximately 1µs and the device then returns to the Read Mode without changing data in the block. If an attempt is made to erase a protected block, DQ7 outputs complement data in approximately 100us and the device then returns to the Read Mode without erasing the data in the block.

**DQ6 : Toggle Bit**

Toggle bit is another option to detect whether an Internal Routine is in progress or completed. Once the device is at a busy state, DQ6 will toggle. Toggling DQ6 will stop after the device completes its Internal Routine. If the device is in the Erase/Program Suspend Mode, an attempt to read an address that belongs to a block that is being erased or programmed will produce a high output of DQ6. If an address belongs to a block that is not being erased or programmed, toggling is halted and valid data is produced at DQ6. If an attempt is made to program a protected block, DQ6 toggles for approximately 1us and the device then returns to the Read Mode without changing the data in the block. If an attempt is made to erase a protected block, DQ6 toggles for approximately 100µs and the device then returns to the Read Mode without erasing the data in the block. #OE or #CE should be toggled in each toggle bit status read.

**DQ5 : Exceed Timing Limits**

If the Internal Program/Erase Routine extends beyond the timing limits, DQ5 will go High, indicating program/erase failure.

**DQ3 : Block Erase Timer**

The status of the multi-block erase operation can be detected via the DQ3 pin. DQ3 will go High if 50µs of the block erase time window expires. In this case, the Internal Erase Routine will initiate the erase operation. Therefore, the device will not accept further write commands until the erase operation is completed. DQ3 is Low if the block erase time window is not expired. Within the block erase time window, an additional block erase command (30H) can be accepted. To confirm that the block erase command has been accepted, the software may check the status of DQ3 following each block erase command.

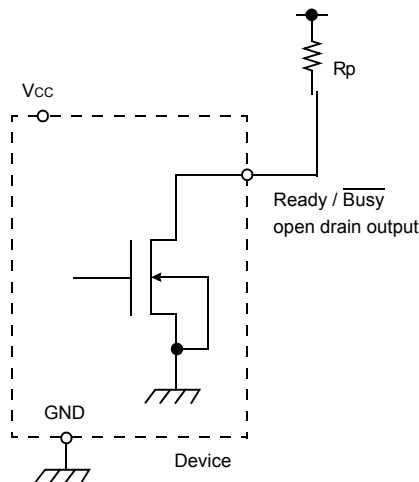
**DQ2 : Toggle Bit 2**

The device generates a toggling pulse in DQ2 only if an Internal Erase Routine or an Erase/Program Suspend is in progress. When the device executes the Internal Erase Routine, DQ2 toggles only if an erasing bank is read. Although the Internal Erase Routine is in the Exceeded Time Limits, DQ2 toggles only if an erasing block in the Exceeded Time Limits is read. When the device is in the Erase/Program Suspend mode, DQ2 toggles only if an address in the erasing or programming block is read. If a non-erasing or non-programmed block address is read during the Erase/Program Suspend mode, then DQ2 will produce valid data. DQ2 will go High if the user tries to program a non-erase suspend block while the device is in the Erase Suspend mode. #OE or #CE should be toggled in each toggle bit status read.

**RY/BY : Ready/Busy**

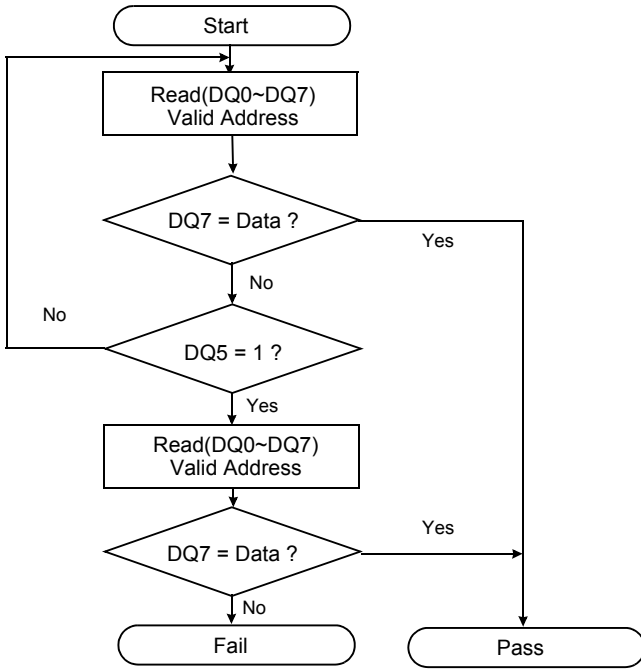
The K8P1615UQB has a Ready / Busy output that indicates either the completion of an operation or the status of Internal Algorithms. If the output is Low, the device is busy with either a program or an erase operation. If the output is High, the device is ready to accept any read/write or erase operation. When the RY/ BY pin is low, the device will not accept any additional program or erase commands with the exception of the Erase Suspend command. If the K8P1615UQB is placed in an Erase Suspend mode, the RY/ BY output will be High. For programming, the RY/ BY is valid (RY/ BY = 0) after the rising edge of the fourth WE pulse in the four write pulse sequence. For Chip Erase, RY/ BY is also valid after the rising edge of WE pulse in the six write pulse sequence. For Block Erase, RY/ BY is also valid after the rising edge of the sixth WE pulse.

The pin is an open drain output, allowing two or more Ready/ Busy outputs to be OR-tied. An appropriate pull-up resistor is required for proper operation.

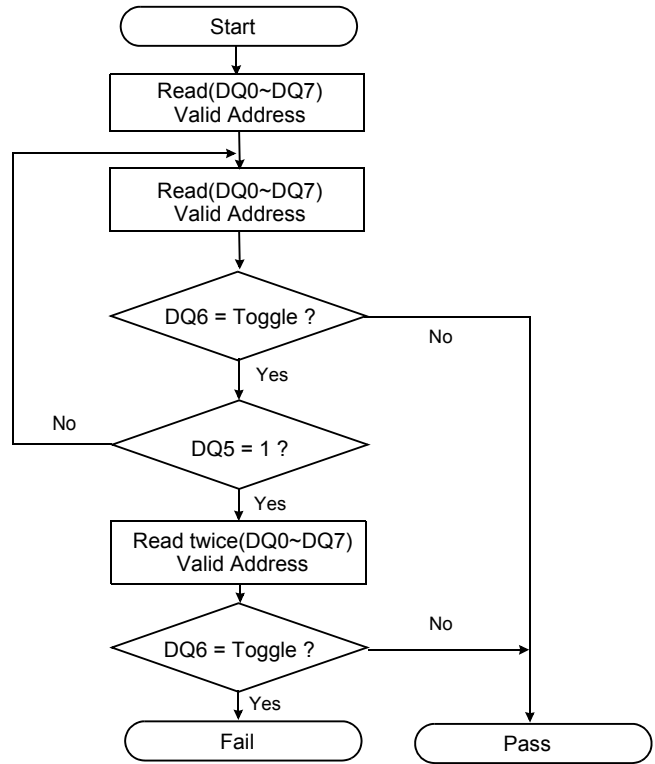


$$R_p = \frac{V_{cc} (\text{Max.}) - V_{OL} (\text{Max.})}{I_{OL} + \sum I_L} = \frac{3.2 \text{ V}}{2.1\text{mA} + \sum I_L}$$

where  $\sum I_L$  is the sum of the input currents of all devices tied to the Ready / Busy pin.



**Figure 9. Data Polling Algorithms**



**Figure 10. Toggle Bit Algorithms**

**K8P1615UQB**

**FLASH MEMORY**

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Rating	Unit
Voltage on any pin relative to Vss	Vcc	-0.5 to +4.0	V
	A9, RESET	-0.5 to +9.5	
	WP/ACC	-0.5 to +9.5	
	All Other Pins	-0.5 to +2.5	
Temperature Under Bias	Commercial	-10 to +125	°C
	Extended	-25 to +125	
Storage Temperature	Tstg	-65 to +150	°C
Short Circuit Output Current	Ios	5	mA
Operating Temperature	TA (Commercial)	0 to +70	°C
	TA (Extended Temp.)	-25 to +85	°C

**Notes :**

- Minimum DC voltage is -0.5V on Input/ Output pins. During transitions, this level may fall to -2.0V for periods <20ns. Maximum DC voltage on input / output pins is Vcc+0.5V which, during transitions, may overshoot to Vcc+2.0V for periods <20ns.
- Minimum DC voltage is -0.5V on A9, RESET and WP/ACC pins. During transitions, this level may fall to -2.0V for periods <20ns. Maximum DC voltage on A9, RESET, WP/ACC pins is 9.5V which, during transitions, may overshoot to 14.0V for periods <20ns.
- Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**RECOMMENDED OPERATING CONDITIONS ( Voltage reference to GND )**

Parameter	Symbol	Min	Typ.	Max	Unit
Supply Voltage	Vcc	2.7	3.0	3.6	V
Supply Voltage	Vss	0	0	0	V

**DC CHARACTERISTICS**

Parameter	Sym- bol	Test Conditions	Min	Typ	Max	Unit	
Input Leakage Current	ILI	VIN=VSS to VCC, VCC=VCCmax	- 1.0	-	+ 1.0	µA	
A9,RESET Input Leakage Current	ILIT	VCC=VCCmax, A9, RESET=9.5V	-	-	35	µA	
WP/ACC Input Leakage Current	ILIW	VCC=VCCmax, WP/ACC=9.5V	-	-	35	µA	
Output Leakage Current	ILO	VOUT=VSS to VCC,VCC=VCC-max,OE=VIH	- 1.0	-	+ 1.0	µA	
Active Read Current (1)	Icc1	OE=VIH, VCC=VCCmax	10MHz	-	45	55	mA
			5MHz	-	20	30	
Active Write Current (2)	Icc2	CE=VIL, OE=VIH, WE=VIL	-	15	30	mA	
Read While Program Current (3)	Icc3	CE=VIL, OE=VIH (@10Mhz)	-	35	55	mA	
Read While Erase Current (3)	Icc4	CE=VIL, OE=VIH (@10Mhz)	-	35	55	mA	
Program While Erase Suspend Current	Icc5	CE=VIL, OE=VIH	-	15	35	mA	
Page Read Current	Icc6	OE=VIH, 8 word Page Read	-	10	15	mA	
ACC Accelerated Program Current	Iacc	CE=VIL, OE=VIH	-	15	30	mA	
Standby Current	ISB1	CE, RESET, WP/ACC= VIO± 0.3	-	15	30	µA	
Standby Current During Reset	ISB2	RESET= Vss± 0.3	-	15	30	µA	
Automatic Sleep Mode	ISB3	VIH=VIO ± 0.3V, VIL=Vss ±0.2V	-	15	30	µA	
Input Low Level	VIL	Vio=1.65~1.95V(2.7~3.6V)	-0.4(-0.5)	-	0.4 (Vccx0.2)	V	
Input High Level	VIH	Vio=1.65~1.95V(2.7~3.6V)	Vio -0.4 (Vccx0.8)	-	Vio+0.4 (Vcc+0.3)	V	
Voltage for WP/ACC Block Temporarily Unprotect and Program Acceleration (4)	VHH	Vcc = 3.0V ± 0.15V	8.5	-	9.5	V	

**K8P1615UQB**

**FLASH MEMORY**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Voltage for Autoselect and Block Protect (4)	V <sub>ID</sub>	V <sub>CC</sub> = 3.0V ± 10%	8.5	-	9.5	V
Output Low Level	V <sub>OL</sub>	IOL = 100uA, V <sub>CC</sub> =V <sub>CCmin</sub> , V <sub>IO</sub> =1.65~1.95V	-	-	0.1	V
		IOL = 2.0mA, V <sub>CC</sub> =V <sub>CCmin</sub> , V <sub>IO</sub> =2.7~3.6V	-	-	0.4	V
Output High Level	V <sub>OH</sub>	I <sub>OH</sub> = -100uA, V <sub>CC</sub> =V <sub>CCmin</sub> , V <sub>IO</sub> =1.65~1.95V	V <sub>IO</sub> -0.1	-	-	V
		I <sub>OH</sub> = -2.0mA, V <sub>CC</sub> =V <sub>CCmin</sub> , V <sub>IO</sub> =2.7~3.6V	2.4	-	-	V
Low VCC Lock-out Voltage (5)	V <sub>LKO</sub>		2.3	-	2.5	V

**Notes :**

1. The I<sub>CC</sub> current listed includes both the DC operating current and the frequency dependent component(at 10 MHz).
2. I<sub>CC</sub> active during Internal Routine(program or erase) is in progress.
3. I<sub>CC</sub> active during Read while Write is in progress.
4. The high voltage ( V<sub>HH</sub> or V<sub>ID</sub> ) must be used in the range of V<sub>CC</sub> = 3.0V ± 0.15V
5. Not 100% tested.
6. Typical value are measured at V<sub>CC</sub> = 3.0V, T<sub>A</sub>=25°C , Not 100% tested.

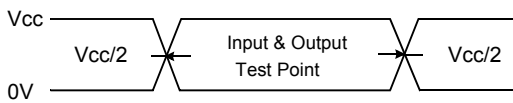
**CAPACITANCE**(T<sub>A</sub> = 25 °C, V<sub>CC</sub> = 3.0V, f = 1.0MHz)

Item	Symbol	Test Condition	Min	Max	Unit
Input Capacitance	C <sub>IN</sub>	V <sub>IN</sub> =0V	-	10	pF
Output Capacitance	C <sub>OUT</sub>	V <sub>OUT</sub> =0V	-	10	pF
Control Pin Capacitance	C <sub>IN2</sub>	V <sub>IN</sub> =0V	-	10	pF

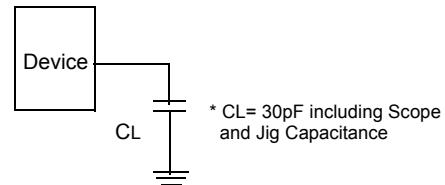
**Note :** Capacitance is periodically sampled and not 100% tested.

**AC TEST CONDITION**

Parameter	Value
Input Pulse Levels	0V to V <sub>CC</sub>
Input Rise and Fall Times(V <sub>IO</sub> =1.8,3.0V)	5ns
Input and Output Timing Levels	V <sub>CC</sub> /2
Output Load	C <sub>L</sub> = 30pF



**Input Pulse and Test Point**



**Output Load**

**AC CHARACTERISTICS**

**Read Operations**

Parameter	Symbol	V <sub>CC</sub> =2.7V~3.6V						Unit
		4B		4C		4D		
		Min	Max	Min	Max	Min	Max	
Read Cycle Time (1)	t <sub>RC</sub>	60	-	65	-	70	-	ns
Address Access Time	t <sub>AA</sub>	-	60	-	65	-	70	ns
Chip Enable Access Time	t <sub>CE</sub>	-	60	-	65	-	70	ns
Output Enable Time	t <sub>OE</sub>	-	25	-	30	-	30	ns
Page Read Cycle Time (1)	t <sub>PRC</sub>	25	-	25	-	30	-	ns
Page Address Access Time	t <sub>PA</sub>	-	25	-	25	-	30	ns
$\overline{\text{CE}}$ & $\overline{\text{OE}}$ Disable Time (1)	t <sub>DF</sub>	-	16	-	16	-	16	ns
Output Hold Time from Address, $\overline{\text{CE}}$ or $\overline{\text{OE}}$ (1)	t <sub>OH</sub>	5	-	5	-	5	-	ns

**Note :** 1. Not 100% tested.



**AC CHARACTERISTICS**  
**Write(Erase/Program)Operations**  
**Alternate WE Controlled Write**

Parameter		Symbol	V <sub>CC</sub> =2.7V~3.6V						Unit
			4B		4C		4D		
			Min	Max	Min	Max	Min	Max	
Write Cycle Time (1)		t <sub>WC</sub>	60	-	65	-	70	-	ns
Address Setup Time		t <sub>AS</sub>	0	-	0	-	0	-	ns
		t <sub>ASO</sub>	15	-	15	-	15	-	ns
Address Hold Time		t <sub>AH</sub>	35	-	35	-	35	-	ns
		t <sub>AHT</sub>	0	-	0	-	0	-	ns
Data Setup Time		t <sub>DS</sub>	30	-	30	-	30	-	ns
Data Hold Time		t <sub>DH</sub>	0	-	0	-	0	-	ns
Output Enable Setup Time (1)		t <sub>OES</sub>	0	-	0	-	0	-	ns
Output Enable Hold Time	Read (1)	t <sub>OE1</sub>	0	-	0	-	0	-	ns
	Toggle and $\overline{\text{Data}}$ Polling (1)	t <sub>OE2</sub>	10	-	10	-	10	-	ns
$\overline{\text{CE}}$ Setup Time		t <sub>Cs</sub>	0	-	0	-	0	-	ns
$\overline{\text{CE}}$ Hold Time		t <sub>CH</sub>	0	-	0	-	0	-	ns
Write Pulse Width		t <sub>WP</sub>	35	-	35	-	35	-	ns
Write Pulse Width High		t <sub>WPH</sub>	25	-	25	-	25	-	ns
Programming Operation		t <sub>PGM</sub>	6(typ)		6(typ.)		6(typ.)		μs
Accelerated Programming Operation		t <sub>ACCPGM</sub>	6(typ)		6(typ.)		6(typ.)		μs
Accelerated Quad word Programming Operation		t <sub>ACCPGM_QUAD</sub>	1.5(typ.)		1.5(typ.)		1.5(typ.)		μs
Block Erase Operation (2)		t <sub>BERS</sub>	0.7(typ)		0.7(typ.)		0.7(typ.)		sec
V <sub>CC</sub> Set Up Time		t <sub>VCS</sub>	50	-	50	-	50	-	μs
Write Recovery Time from RY/ $\overline{\text{BY}}$		t <sub>RB</sub>	0	-	0	-	0	-	ns
$\overline{\text{RESET}}$ High Time Before Read		t <sub>RH</sub>	50	-	50	-	50	-	ns
$\overline{\text{RESET}}$ to Power Down Time		t <sub>RPD</sub>	20	-	20	-	20	-	μs
Program/Erase Valid to RY/ $\overline{\text{BY}}$ Delay		t <sub>BUSY</sub>	35	90	35	90	35	90	ns
V <sub>ID</sub> Rising and Falling Time		t <sub>VID</sub>	500	-	500	-	500	-	ns
$\overline{\text{RESET}}$ Pulse Width		t <sub>RP</sub>	500	-	500	-	500	-	ns
$\overline{\text{RESET}}$ Low to RY/ $\overline{\text{BY}}$ High		t <sub>RRB</sub>	-	20	-	20	-	20	μs
$\overline{\text{RESET}}$ Setup Time for Temporary Unprotect		t <sub>RSP</sub>	4	-	4	-	4	-	μs
$\overline{\text{RESET}}$ Low Setup Time		t <sub>RSTS</sub>	500	-	500	-	500	-	ns
$\overline{\text{RESET}}$ High to Address Valid		t <sub>RSTW</sub>	200	-	200	-	200	-	ns
Read Recovery Time Before Write		t <sub>GHWL</sub>	0	-	0	-	0	-	ns
$\overline{\text{CE}}$ High during toggling bit polling		t <sub>CEPH</sub>	20	-	20	-	20	-	ns
$\overline{\text{OE}}$ High during toggling bit polling		t <sub>OEPH</sub>	10	-	10	-	10	-	ns

Notes : 1. Not 100% tested.  
 2. The duration of the Program or Erase operation varies and is calculated in the internal algorithms.

**AC CHARACTERISTICS**

**Write(Erase/Program)Operations**

**Alternate CE Controlled Writes**

Parameter	Symbol	Vcc=2.7V~3.6V						Unit	
		4B		4C		4D			
		Min	Max	Min	Max	Min	Max		
Write Cycle Time (1)	tWC	60	-	65	-	70	-	ns	
Address Setup Time	tAS	0	-	0	-	0	-	ns	
Address Hold Time	tAH	35	-	35	-	35	-	ns	
Data Setup Time	tDS	30	-	30	-	30	-	ns	
Data Hold Time	tDH	0	-	0	-	0	-	ns	
Output Enable Setup Time (1)	tOES	0	-	0	-	0	-	ns	
Output Enable Hold Time	Read (1)	tOE1	0	-	0	-	0	-	ns
	Toggle and Data Polling (1)	tOE2	10	-	10	-	10	-	ns
WE Setup Time	tWS	0	-	0	-	0	-	ns	
WE Hold Time	tWH	0	-	0	-	0	-	ns	
CE Pulse Width	tCP	40	-	40	-	40	-	ns	
CE Pulse Width High	tCPH	25	-	25	-	25	-	ns	
Programming Operation	tPGM	6(typ)		6(typ.)		6(typ.)		μs	
Accelerated Programming Operation	tACCPGM	6(typ)		6typ.)		6(typ.)		μs	
Accelerated Quad word Programming Operation	tACCPGM_QUAD	1.5(typ.)		1.5(typ.)		1.5(typ.)		μs	
Block Erase Operation (2)	tBERS	0.7(typ)		0.7typ.)		0.7(typ.)		sec	

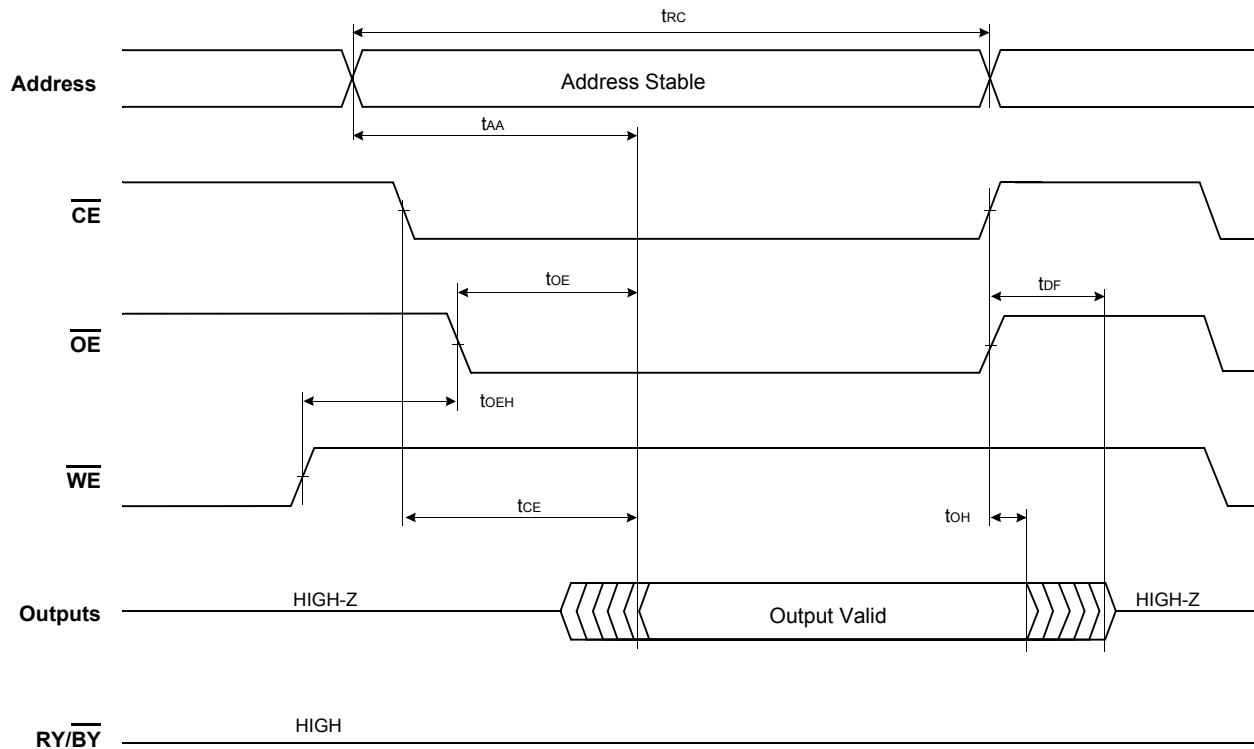
Notes : 1. Not 100% tested.  
2.This does not include the preprogramming time.

**ERASE AND PROGRAM PERFORMANCE**

Parameter	Limits			Unit	Comments
	Min	Typ	Max		
Block Erase Time	-	0.7	2	sec	Excludes 00H programming prior to erasure
Chip Erase Time	-	19.5	31.2	sec	
Word Programming Time	-	6	100	μs	Excludes system-level overhead
Accelerated Word Program Time	-	6	100	μs	
Accelerated Quad Word Program Time	-	1.5	-	μs	
Chip Programming Time (Normal)	-	6.3	12.6	sec	
Chip Programming Time (Acc. Quad)	-	1.5	-	sec	
Erase/Program Endurance	100,000	-	-	cycles	Minimum 100,000 cycles guaranteed

Notes : 1. 25 °C, Vcc = 3.0V 100,000 cycles, typical pattern.  
2. System-level overhead is defined as the time required to execute the four bus cycle command necessary to program each word. In the preprogramming step of the Internal Erase Routine, all words are programmed to 00H before erasure.

**SWITCHING WAVEFORMS**  
**Conventional Read Operations**



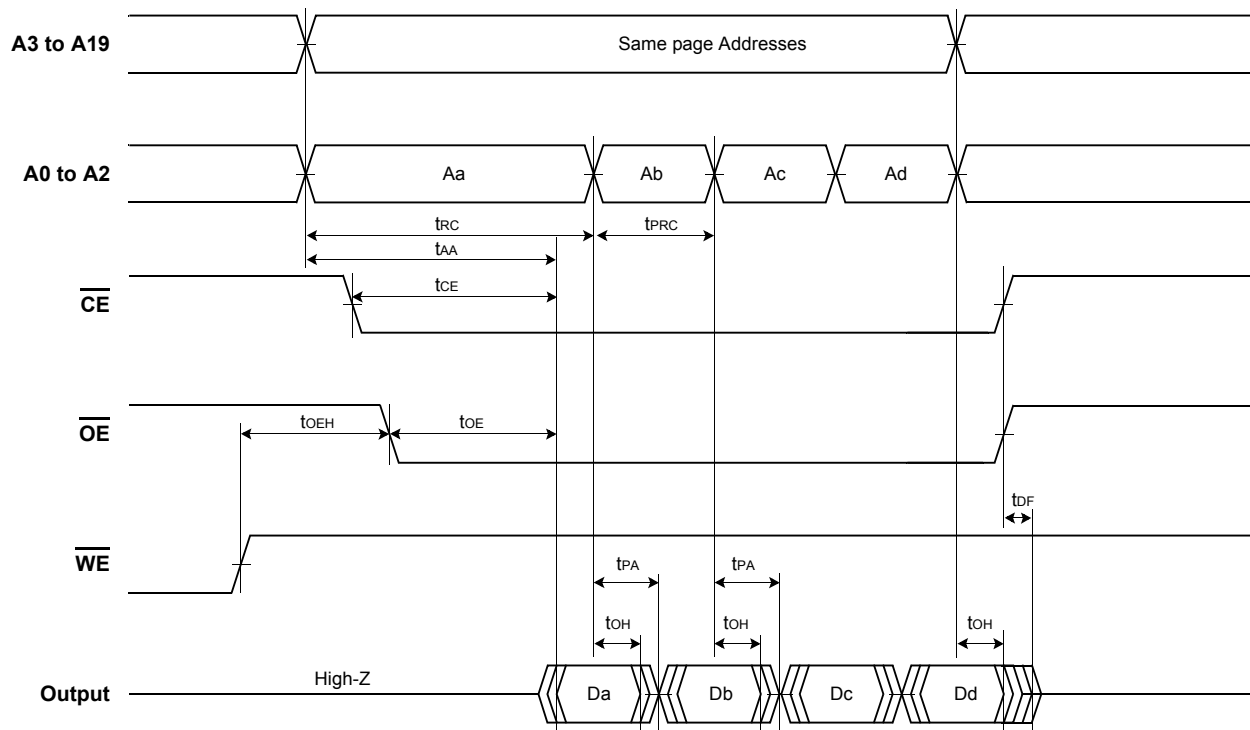
**Figure 11. Conventional Read Operation Timings**

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	$t_{RC}$	60	-	65	-	70	-	ns
Address Access Time	$t_{AA}$	-	60	-	65	-	70	ns
Chip Enable Access Time	$t_{CE}$	-	60	-	65	-	70	ns
Output Enable Time	$t_{OE}$	-	25	-	30	-	30	ns
$\overline{CE}$ & $\overline{OE}$ Disable Time (1)	$t_{DF}$	-	16	-	16	-	16	ns
Output Hold Time from Address, $\overline{CE}$ or $\overline{OE}$	$t_{OH}$	5	-	5	-	5	-	ns
$\overline{OE}$ Hold Time	$t_{OEH}$	0	10	0	10	0	10	ns

Note : 1. Not 100% tested.

**SWITCHING WAVEFORMS**

**Page Read Operations**



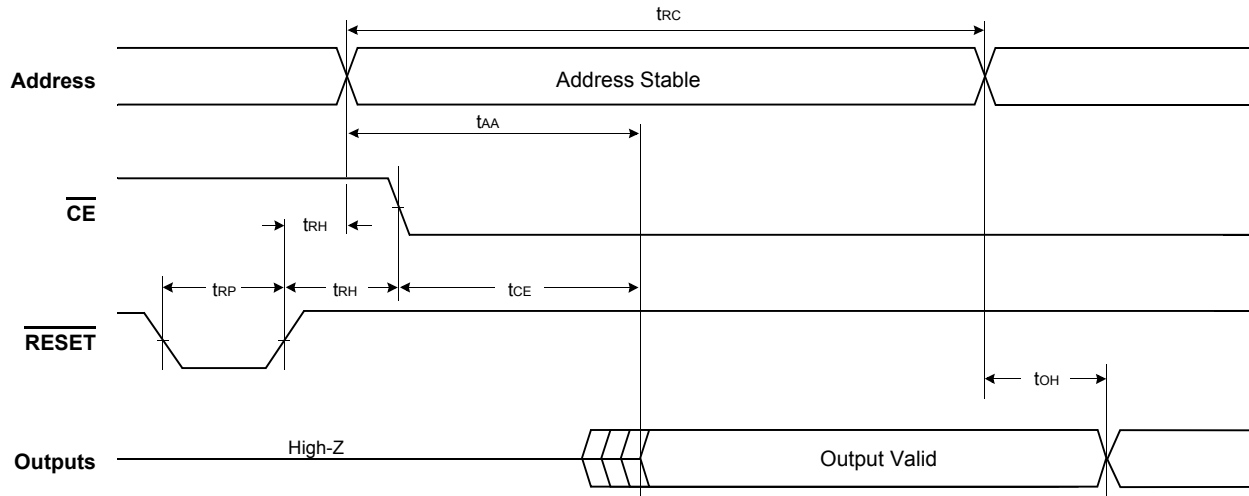
**Figure 12. Page Read Operation Timings**

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	tRC	60	-	65	-	70	-	ns
Page Read Cycle Time	tPRC	25	-	25	-	30	-	ns
Address Access Time	tAA	-	60	-	65	-	70	ns
Page Address Access Time	tPA	-	25	-	25	-	30	ns
Chip Enable Access Time	tCE	-	60	-	65	-	70	ns
Output Enable Time	tOE	-	25	-	30	-	30	ns
CE & OE Disable Time (1)	tDF	-	16	-	16	-	16	ns
Output Hold Time from Address, CE or OE	tOH	5	-	5	-	5	-	ns
OE Hold Time	tOEH	0	-	0	-	0	-	ns

Note : 1. Not 100% tested.

**SWITCHING WAVEFORMS**

**Hardware Reset/Read Operations**

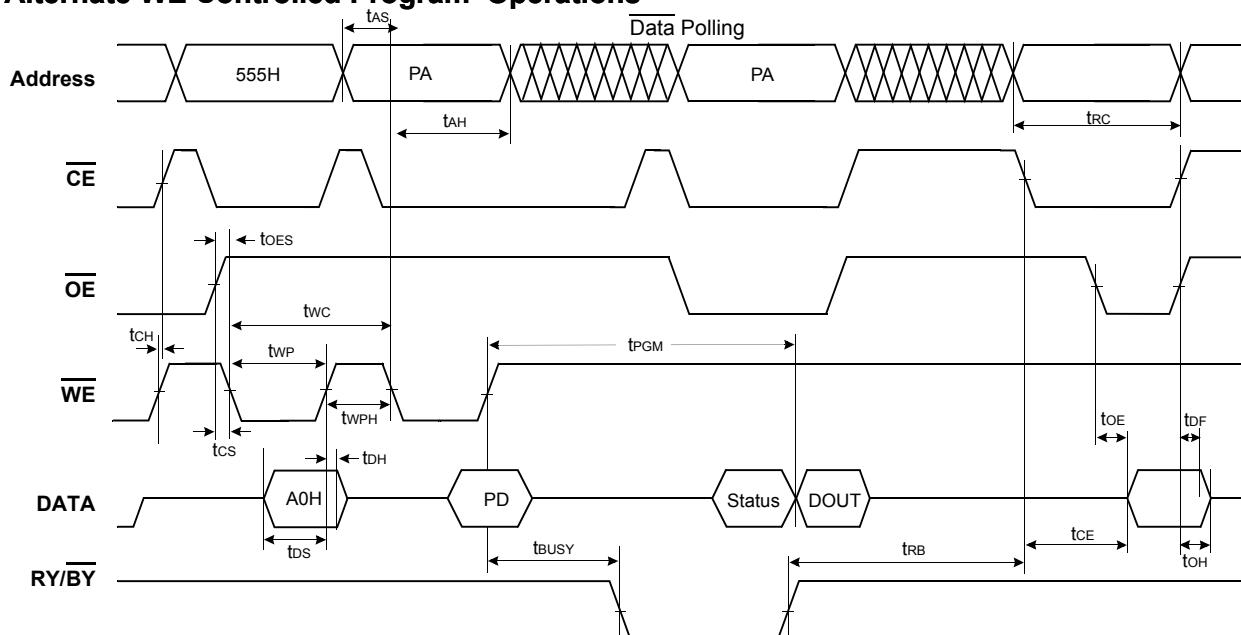


**Figure 13. Hardware Reset/Read Operation Timings**

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Read Cycle Time	$t_{RC}$	60	-	65	-	70	-	ns
Address Access Time	$t_{AA}$	-	60	-	65	-	70	ns
Chip Enable Access Time	$t_{CE}$	-	60	-	65	-	70	ns
Output Hold Time from Address, $\overline{CE}$ or $\overline{OE}$	$t_{OH}$	5	-	5	-	5	-	ns
$\overline{RESET}$ Pulse Width	$t_{RP}$	500	-	500	-	500	-	ns
$\overline{RESET}$ High Time Before Read	$t_{RH}$	50	-	50	-	50	-	ns

SWITCHING WAVEFORMS

Alternate WE Controlled Program Operations



- Notes : 1.  $\overline{DQ7}$  is the output of the complement of the data written to the device.
- 2. DOOUT is the output of the data written to the device.
- 3. PA : Program Address, PD : Program Data
- 4. The illustration shows the last two cycles of the program command sequence.

Figure 14. Alternate WE Controlled Program Operation Timings

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	tWC	60	-	65	-	70	-	ns
Address Setup Time	tAS	0	-	0	-	0	-	ns
Address Hold Time	tAH	35	-	35	-	35	-	ns
Data Setup Time	tDS	30	-	30	-	30	-	ns
Data Hold Time	tDH	0	-	0	-	0	-	ns
$\overline{CE}$ Setup Time	tCS	0	-	0	-	0	-	ns
$\overline{CE}$ Hold Time	tCH	0	-	0	-	0	-	ns
$\overline{OE}$ Setup Time	toES	0	-	0	-	0	-	ns
Write Pulse Width	tWP	35	-	35	-	35	-	ns
Write Pulse Width High	tWPH	25	-	25	-	25	-	ns
Programming Operation	tPBM	6(typ)		6(typ.)		6(typ.)		us
Accelerated Programming Operation	tACCPGM	6(typ)		6(typ.)		6(typ.)		μs
Read Cycle Time	tRC	60	-	65	-	70	-	ns
Chip Enable Access Time	tCE	-	60	-	65	-	70	ns
Output Enable Time	toE	-	25	-	30	-	30	ns
$\overline{CE}$ & $\overline{OE}$ Disable Time	tDF	-	16	-	16	-	16	ns
Output Hold Time from Address, $\overline{CE}$ or $\overline{OE}$	tOH	5	-	5	-	5	-	ns
Program/Erase Valid to $\overline{RY/BY}$ Delay	tBUSY	35	90	35	90	35	90	ns
Recovery Time from $\overline{RY/BY}$	tRB	0	-	0	-	0	-	ns

SWITCHING WAVEFORMS

Alternate  $\overline{\text{CE}}$  Controlled Program Operations

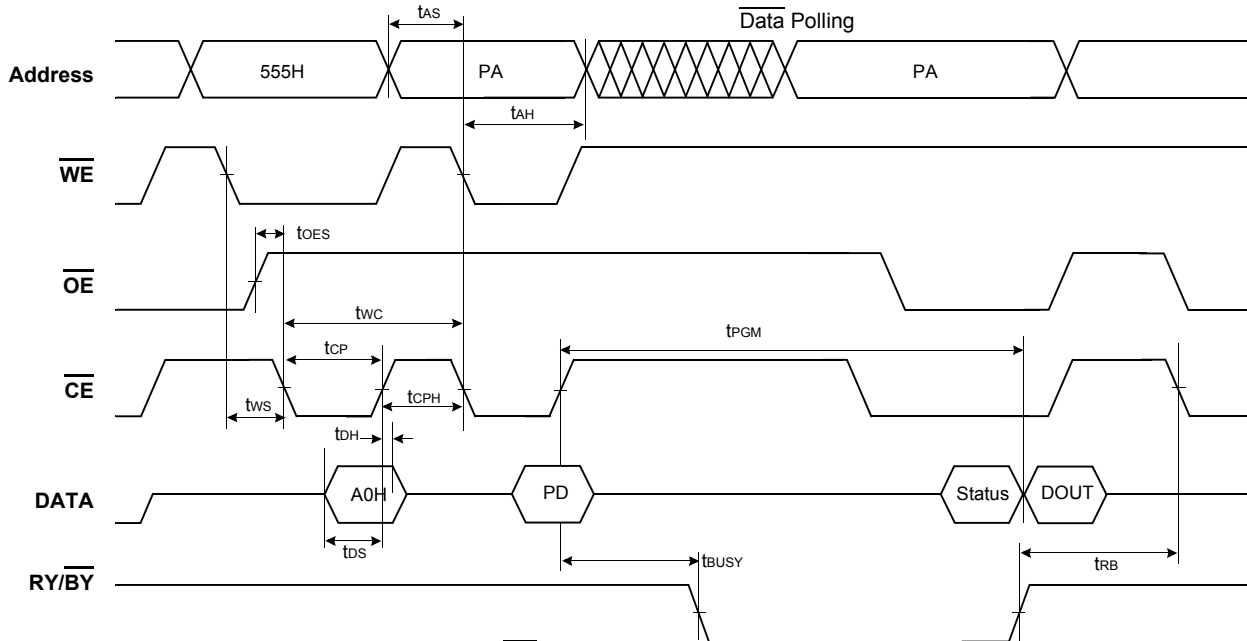


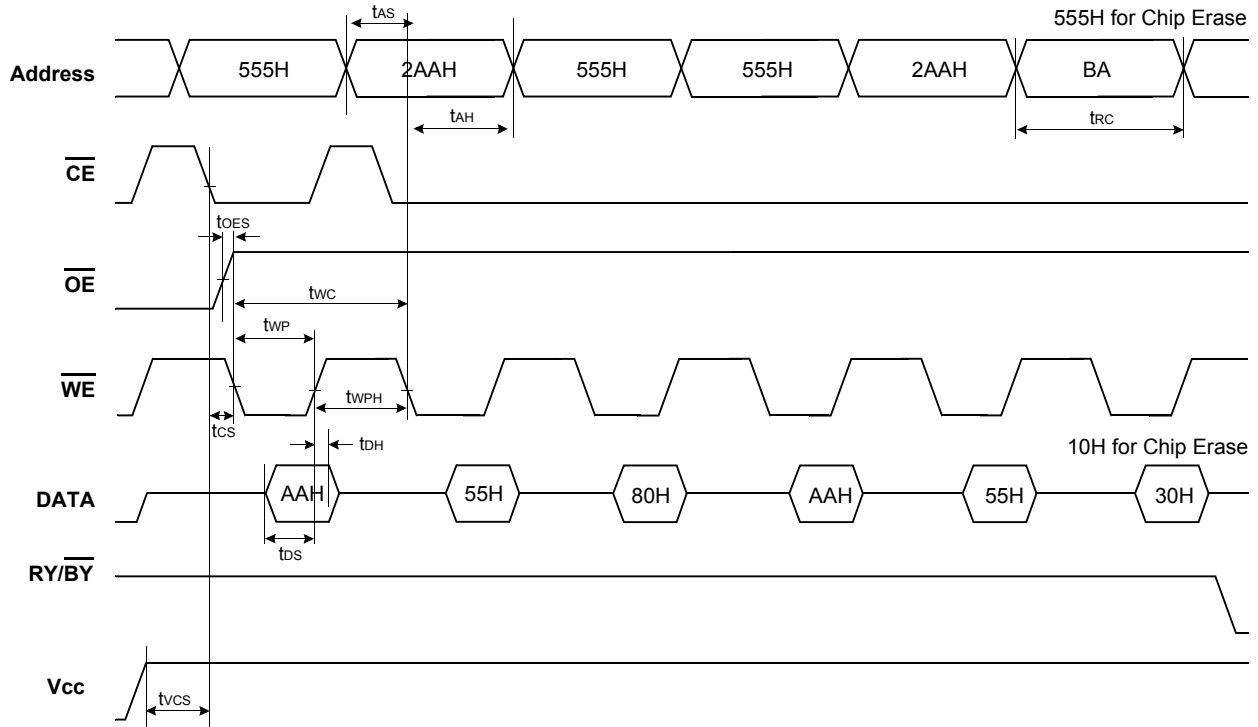
Figure 15. Alternate  $\overline{\text{CE}}$  Controlled Program Operation Timings

Notes :

1.  $\overline{\text{DQ7}}$  is the output of the complement of the data written to the device.
2. DOUT is the output of the data written to the device.
3. PA : Program Address, PD : Program Data
4. The illustration shows the last two cycles of the program command sequence.

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	tWC	60	-	65	-	70	-	ns
Address Setup Time	tAS	0	-	0	-	0	-	ns
Address Hold Time	tAH	35	-	35	-	35	-	ns
Data Setup Time	tDS	30	-	30	-	30	-	ns
Data Hold Time	tDH	0	-	0	-	0	-	ns
$\overline{\text{OE}}$ Setup Time	tOES	0	-	0	-	0	-	ns
$\overline{\text{WE}}$ Setup Time	tWS	0	-	0	-	0	-	ns
$\overline{\text{WE}}$ Hold Time	tWH	0	-	0	-	0	-	ns
$\overline{\text{CE}}$ Pulse Width	tCP	40	-	40	-	40	-	ns
$\overline{\text{CE}}$ Pulse Width High	tCPH	25	-	25	-	25	-	ns
Programming Operation	tPGM	6(typ)		6(typ.)		6(typ.)		$\mu\text{s}$
Accelerated Programming Operation	tACCPGM	6(typ)		6(typ.)		6(typ.)		$\mu\text{s}$
Program/Erase Valid to $\overline{\text{RY/BY}}$ Delay	tBUSY	35	90	35	90	35	90	ns
Recovery Time from $\overline{\text{RY/BY}}$	tRB	0	-	0	-	0	-	ns

**SWITCHING WAVEFORMS**  
**Chip/Block Erase Operations**



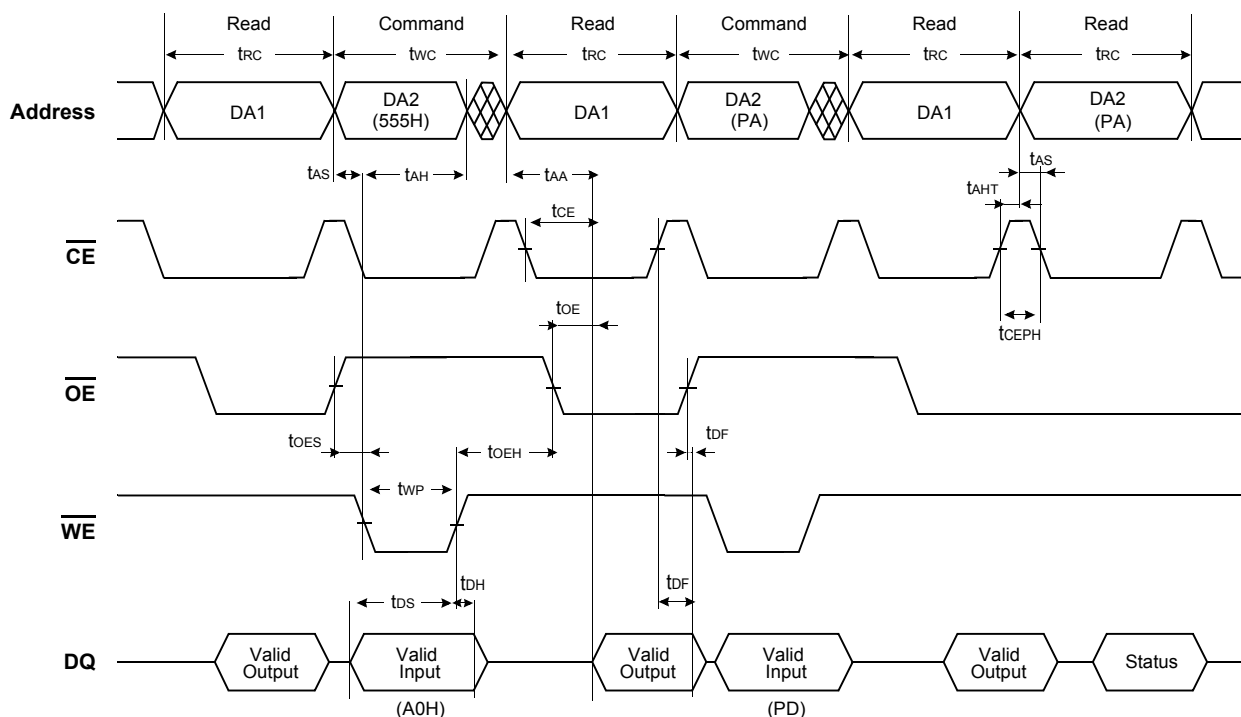
**Figure 16. Chip/Block Erase Operation Timings**

Note : BA : Block Address

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	tWC	60	-	65	-	70	-	ns
Address Setup Time	tAS	0	-	0	-	0	-	ns
Address Hold Time	tAH	35	-	35	-	35	-	ns
Data Setup Time	tDS	30	-	30	-	30	-	ns
Data Hold Time	tDH	0	-	0	-	0	-	ns
$\overline{OE}$ Setup Time	tOES	0	-	0	-	0	-	ns
$\overline{CE}$ Setup Time	tCS	0	-	0	-	0	-	ns
Write Pulse Width	tWP	35	-	35	-	35	-	ns
Write Pulse Width High	tWPH	25	-	25	-	25	-	ns
Read Cycle Time	tRC	60	-	65	-	70	-	ns
Vcc Set Up Time	tVCS	50	-	50	-	50	-	$\mu$ s



**SWITCHING WAVEFORMS**  
**Read While Write Operations**



**Figure 17. Read While Write Operation Timings**

**Note :** This is an example in the program-case of the Read While Write function.

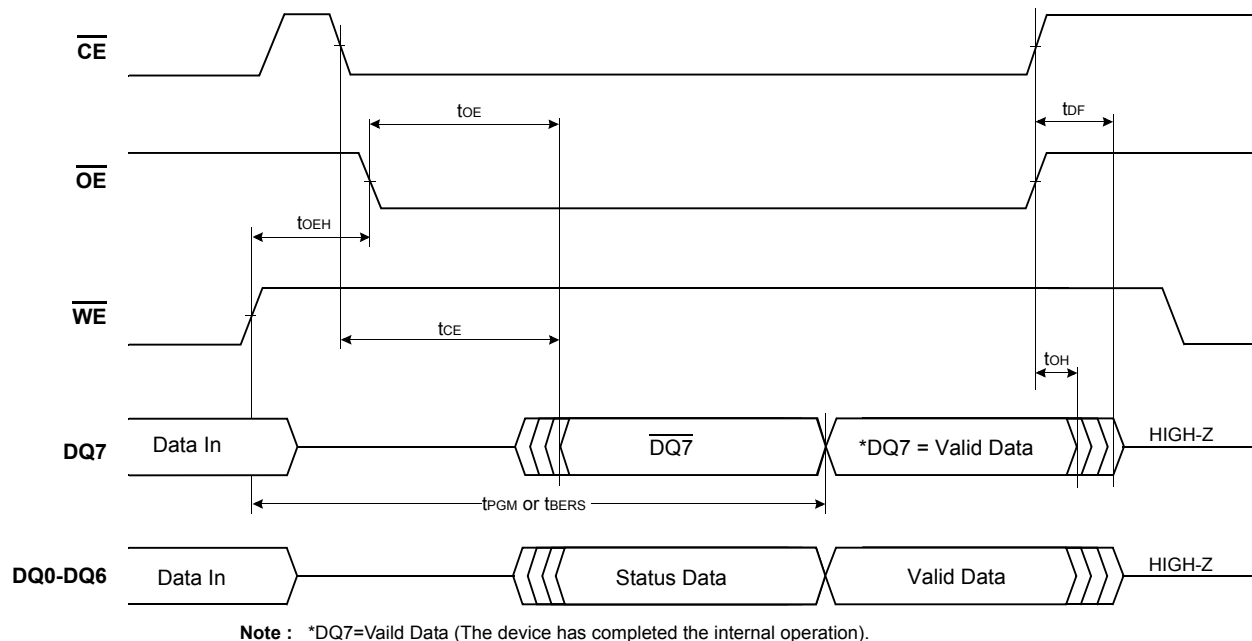
DA1 : Address of Bank1, DA2 : Address of Bank 2

PA = Program Address at one bank , RA = Read Address at the other bank, PD = Program Data In , RD = Read Data Out

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Write Cycle Time	tWC	60	-	65	-	70	-	ns
Write Pulse Width	tWP	35	-	35	-	35	-	ns
Write Pulse Width High	tWPH	25	-	25	-	25	-	ns
Address Setup Time	tAS	0	-	0	-	0	-	ns
Address Hold Time	tAH	35	-	35	-	35	-	ns
Data Setup Time	tDS	30	-	30	-	30	-	ns
Data Hold Time	tDH	0	-	0	-	0	-	ns
Read Cycle Time	tRC	60	-	65	-	70	-	ns
Chip Enable Access Time	tCE	-	60	-	65	-	70	ns
Address Access Time	tAA	-	60	-	65	-	70	ns
Output Enable Access Time	tOE	-	25	-	30	-	30	ns
$\overline{OE}$ Setup Time	tOES	0	-	0	-	0	-	ns
$\overline{OE}$ Hold Time	tOEH	10	-	10	-	10	-	ns
$\overline{CE}$ & $\overline{OE}$ Disable Time	tDF	-	16	-	16	-	16	ns
Address Hold Time	tAHT	35	-	35	-	35	-	ns
$\overline{CE}$ High during toggle bit polling	tCEPH	20	-	20	-	20	-	ns

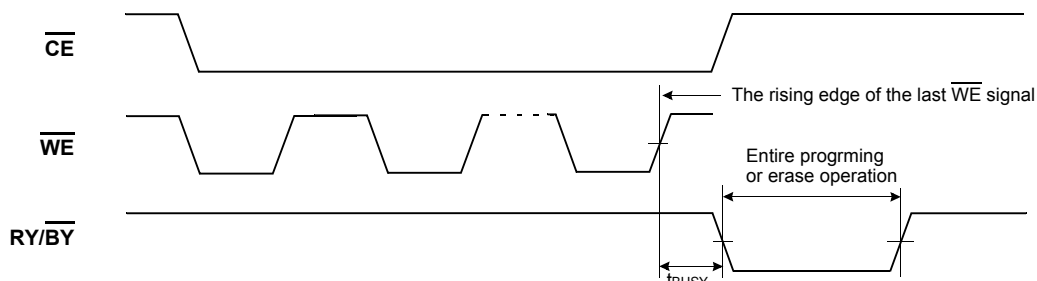
**SWITCHING WAVEFORMS**

**Data Polling During Internal Routine Operation**



**Figure 18. Data Polling During Internal Routine Operation Timings**

**RY/BY Timing Diagram During Program/Erase Operation**

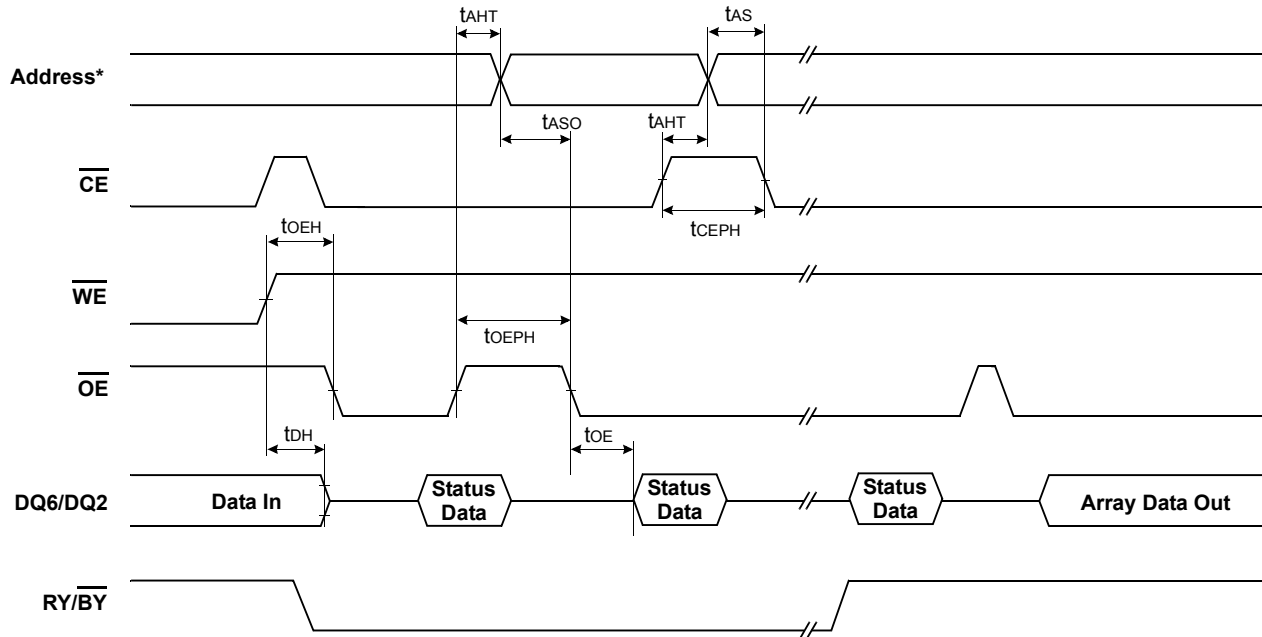


**Figure 19. RY/BY Timing Diagram During Program/Erase Operation Timings**

Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Program/Erase Valid to RY/BY Delay	t <sub>BUSY</sub>	35	90	35	90	35	90	ns
Chip Enable Access Time	t <sub>CE</sub>	-	60	-	65	-	70	ns
Output Enable Time	t <sub>OE</sub>	-	25	-	30	-	30	ns
CE & OE Disable Time	t <sub>DF</sub>	-	16	-	16	-	16	ns
Output Hold Time from Address, CE or OE	t <sub>OH</sub>	5	-	5	-	5	-	ns
OE Hold Time	t <sub>OEH</sub>	10	-	10	-	10	-	ns

SWITCHING WAVEFORMS

Toggle Bit During Internal Routine Operation



Note : Address for the write operation must include a bank address (A17~A19) where the data is written.

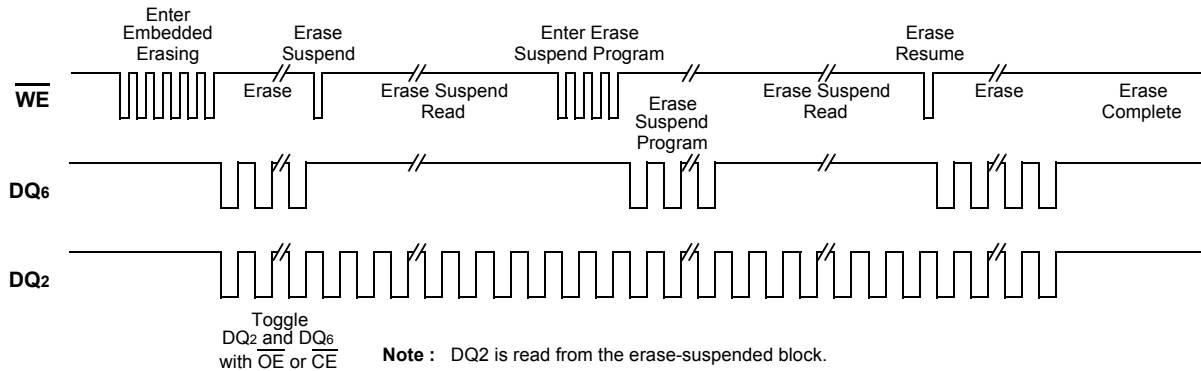
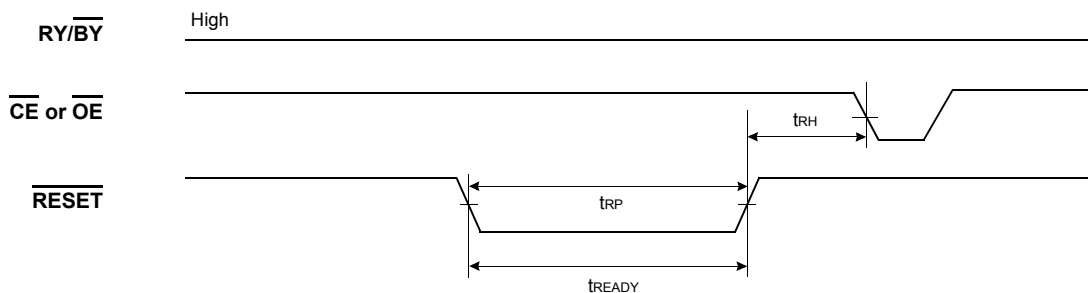


Figure 20. Toggle Bit During Internal Routine Operation Timings

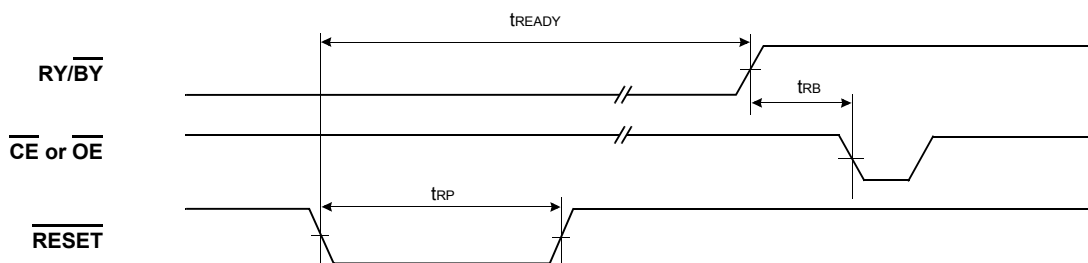
Parameter	Symbol	4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	
Output Enable Access Time	tOE	-	25	-	30	-	30	ns
OE Hold Time	tOEHL	10	-	10	-	10	-	ns
Address Hold Time	tAHT	35	-	35	-	35	-	ns
Address Setup	tASO	55	-	55	-	55	-	ns
Address Setup Time	tAS	0	-	0	-	0	-	ns
Data Hold Time	tDH	0	-	0	-	0	-	ns
CE High during toggle bit polling	tCEPH	20	-	20	-	20	-	ns
OE High during toggle bit polling	tOEPH	10	-	10	-	10	-	ns

**SWITCHING WAVEFORMS**

**RESET Timing Diagram**

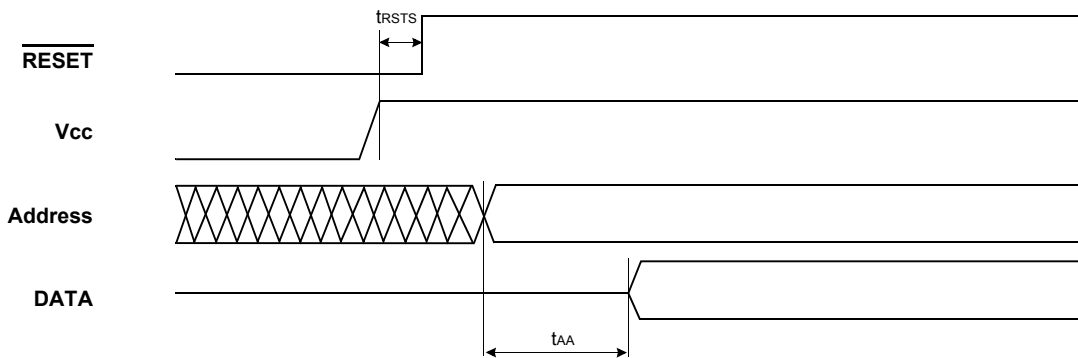


**Reset Timings NOT during Internal Routine**



**Reset Timings during Internal Routine**

**Power-up and RESET Timing Diagram**

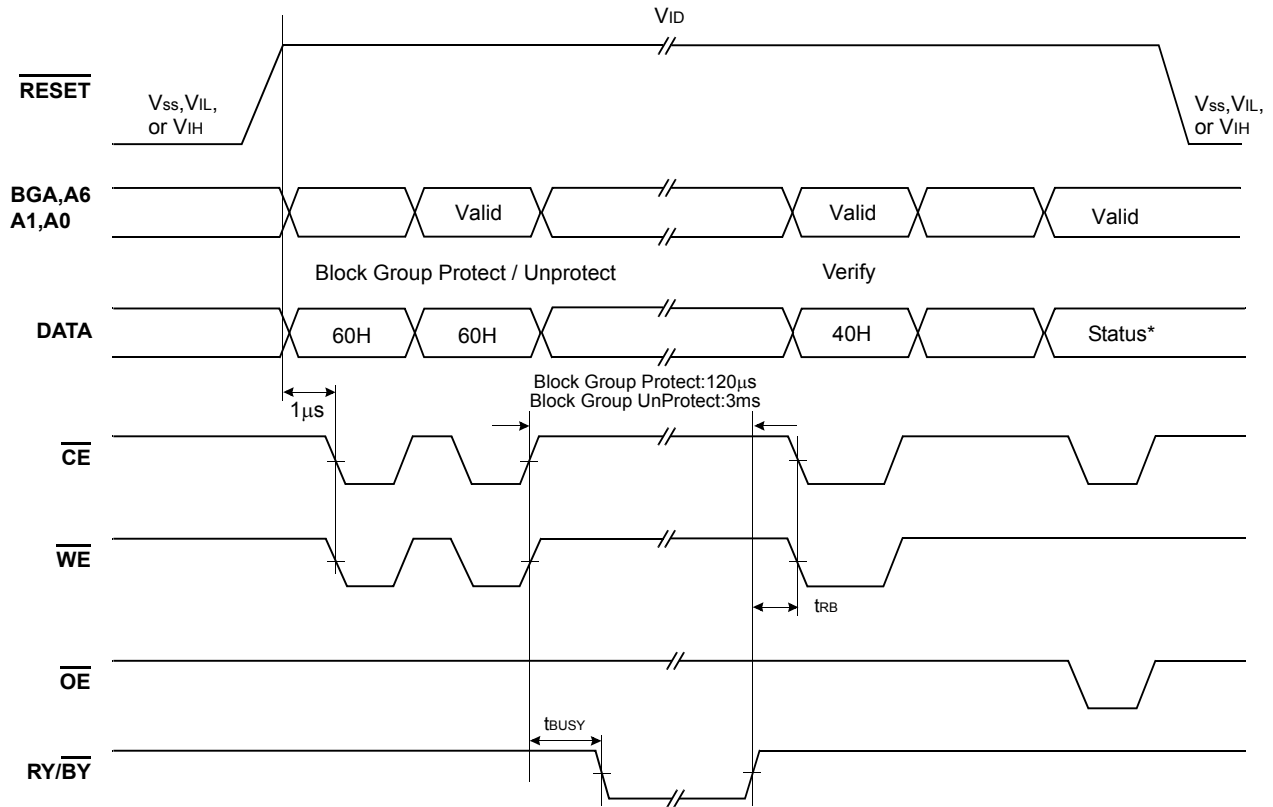


**Figure 21. Power-up and RESET Timing Diagram**

Parameter	Sym- bol	4A		4B		4C		4D		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
RESET Pulse Width	trP	500	-	500	-	500	-	500	-	ns
RESET Low to Valid Data (During Internal Routine)	tREADY	-	20	-	20	-	20	-	20	μs
RESET Low to Valid Data (Not during Internal Routine)	tREADY	-	500	-	500	-	500	-	500	ns
RESET High Time Before Read	trH	50	-	50	-	50	-	50	-	ns
RY/BY Recovery Time	trB	0	-	0	-	0	-	0	-	ns
RESET High to Address Valid	trSTW	200	-	200	-	200	-	200	-	ns
RESET Low Set-up Time	trSTS	500	-	500	-	500	-	500	-	ns

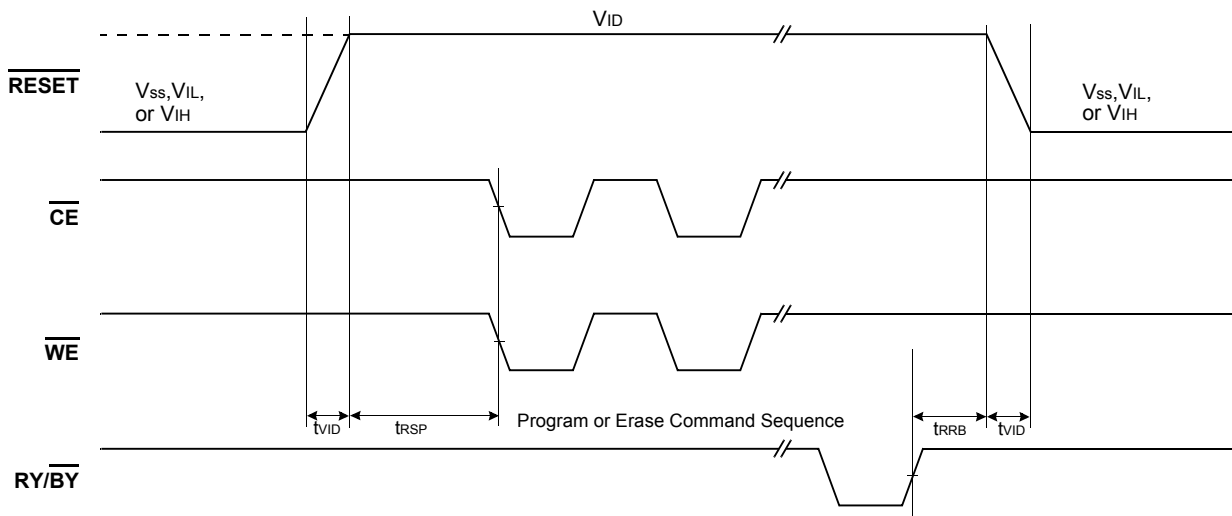
**SWITCHING WAVEFORMS**

**Block Group Protect & Unprotect Operations**



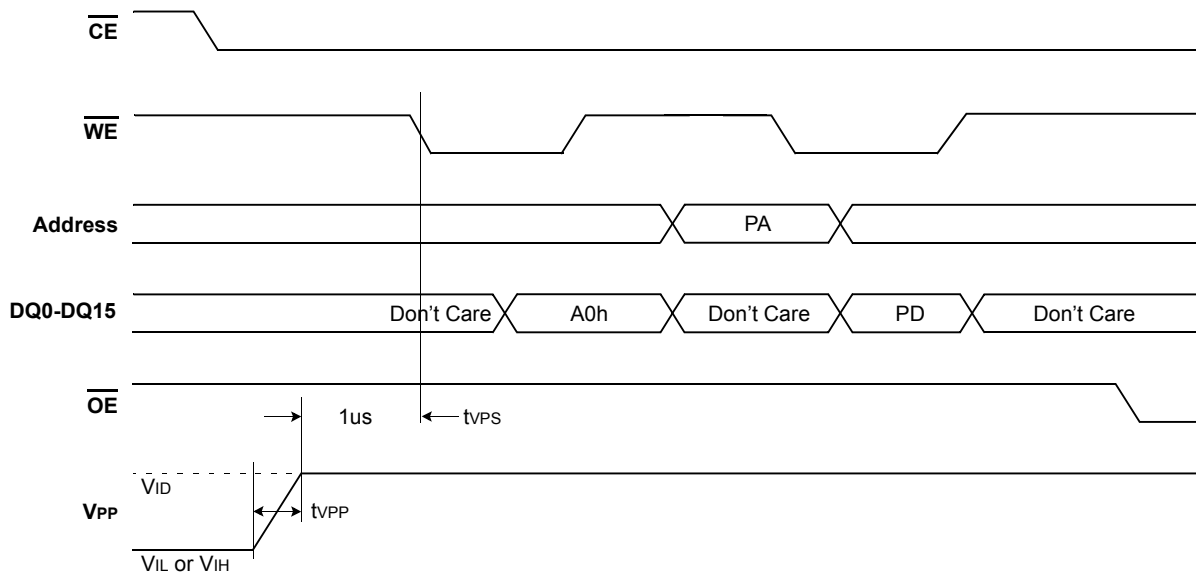
Notes : Block Group Protect (A6=V<sub>IL</sub>, A1=V<sub>IH</sub>, A0=V<sub>IL</sub>), Status=01H  
 Block Group Unprotect (A6=V<sub>IH</sub>, A1=V<sub>IH</sub>, A0=V<sub>IL</sub>), Status=00H  
 BGA = Block Group Address (A12 ~ A19)

**Temporary Block Group Unprotect**

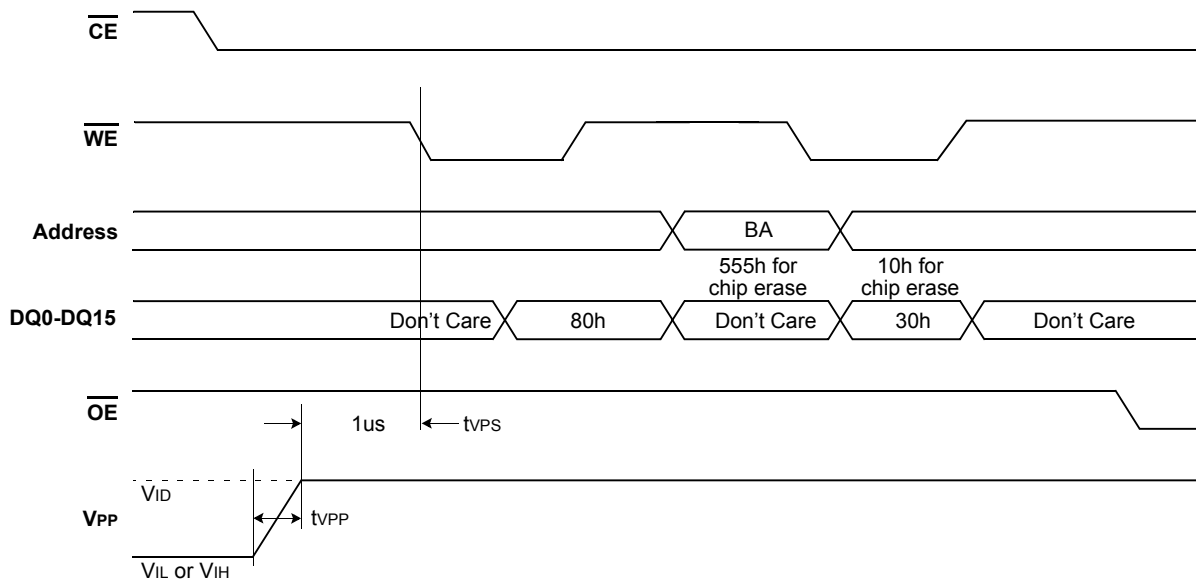


**SWITCHING WAVEFORMS**

**Unlock Bypass Program Operations(Accelerated Program)**



**Unlock Bypass Block Erase Operations**



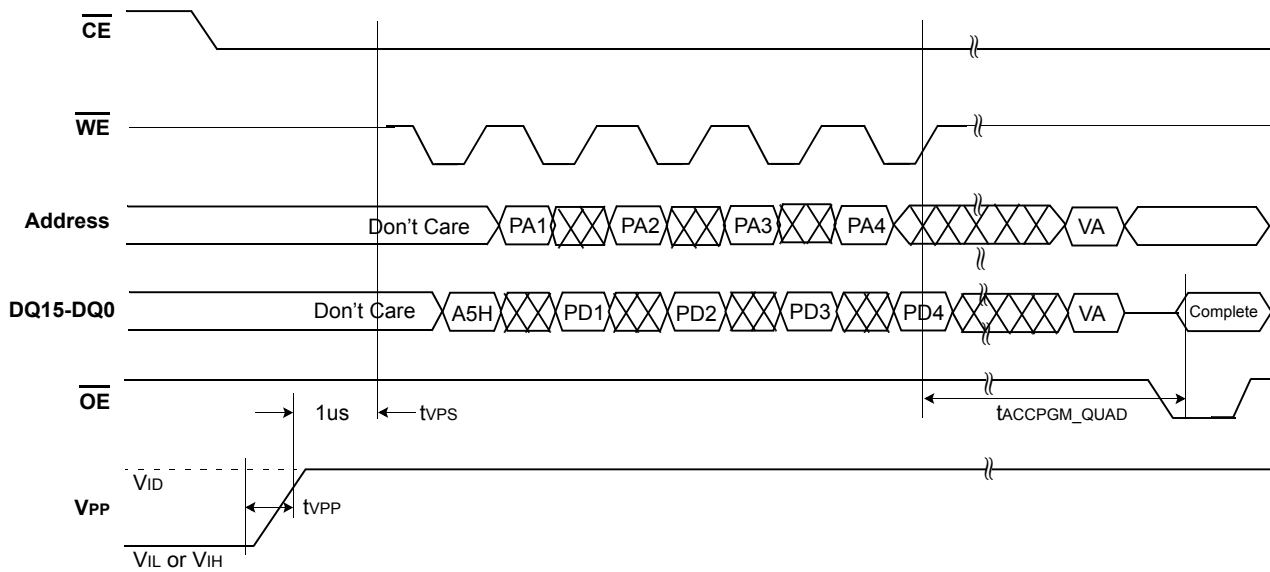
**Notes:**

- 1.  $V_{PP}$  can be left high for subsequent programming pulses.
- 2. Use setup and hold times from conventional program operations.
- 3. Unlock Bypass Program/Erase commands can be used when the  $V_{ID}$  is applied to  $V_{pp}$ .

**Figure 22. Unlock Bypass Operation Timings**

**SWITCHING WAVEFORMS**

**Quad word Accelerated Program**



**Notes:**

- 1.  $V_{PP}$  can be left high for subsequent programming pulses.
- 2. Use setup and hold times from conventional program operations.
- 3. Quad word Accelerate program commands can be used when the  $V_{ID}$  is applied to  $V_{pp}$ .

**Figure 23. Quad word Accelerated Program Operation Timings**

**K8P1615UQB**

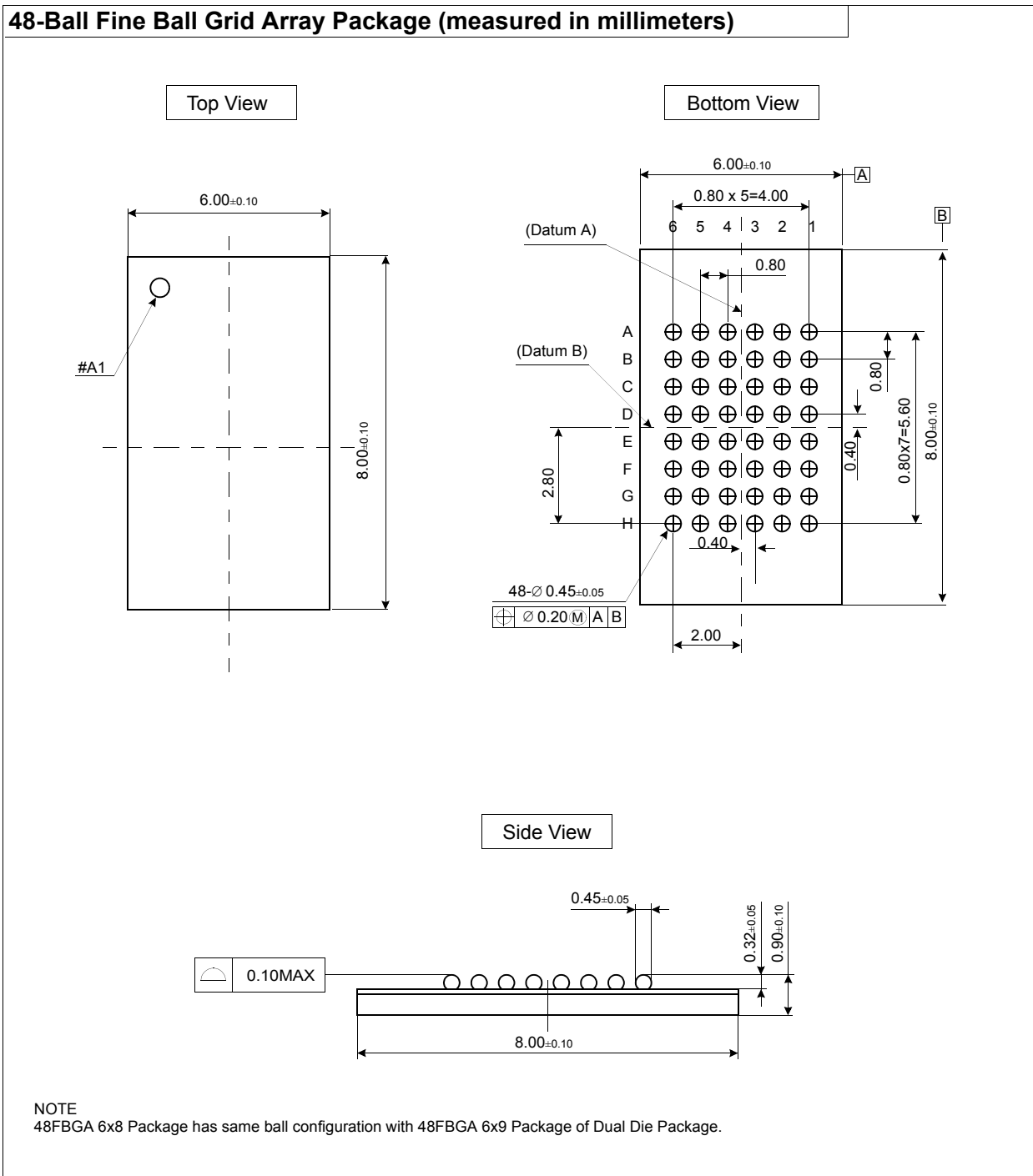
**FLASH MEMORY**

**Table 13. Block Architecture (K8P1615UQB)**

Bank	Block	Block Size	(x16) Address Range
Bank 3	BA45	4 Kwords	FF000h-FFFFFh
	BA44	4 Kwords	FE000h-FEFFFh
	BA43	4 Kwords	FD000h-FDFFFh
	BA42	4 Kwords	FC000h-FCFFFh
	BA41	4 Kwords	FB000h-FBFFFh
	BA40	4 Kwords	FA000h-FAFFFh
	BA39	4 Kwords	F9000h-F9FFFh
	BA38	4 Kwords	F8000h-F8FFFh
	BA37	32 Kwords	F0000h-F7FFFh
	BA36	32 Kwords	E8000h-E7FFFh
Bank2	BA35	32 Kwords	E0000h-E7FFFh
	BA34	32 Kwords	D8000h-D7FFFh
	BA33	32 Kwords	D0000h-D7FFFh
	BA32	32 Kwords	C8000h-C7FFFh
	BA31	32 Kwords	C0000h-C7FFFh
	BA30	32 Kwords	B8000h-B7FFFh
	BA29	32 Kwords	B0000h-B7FFFh
	BA28	32 Kwords	A8000h-A7FFFh
	BA27	32 Kwords	A0000h-A7FFFh
	BA26	32 Kwords	98000h-97FFFh
Bank1	BA25	32 Kwords	90000h-97FFFh
	BA24	32 Kwords	88000h-87FFFh
	BA23	32 Kwords	80000h-87FFFh
	BA22	32 Kwords	78000h-77FFFh
	BA21	32 Kwords	70000h-77FFFh
	BA20	32 Kwords	68000h-67FFFh
	BA19	32 Kwords	60000h-67FFFh
	BA18	32 Kwords	58000h-57FFFh
	BA17	32 Kwords	50000h-57FFFh
	BA16	32 Kwords	48000h-47FFFh
Bank0	BA15	32 Kwords	40000h-47FFFh
	BA14	32 Kwords	38000h-37FFFh
	BA13	32 Kwords	30000h-37FFFh
	BA12	32 Kwords	28000h-27FFFh
	BA11	32 Kwords	20000h-27FFFh
	BA10	32 Kwords	18000h-17FFFh
	BA9	32 Kwords	10000h-17FFFh
	BA8	32 Kwords	08000h-07FFFh
	BA7	4 Kwords	07000h-07FFFh
	BA6	4 Kwords	06000h-06FFFh
BA5	4 Kwords	05000h-05FFFh	
BA4	4 Kwords	04000h-04FFFh	
BA3	4 Kwords	03000h-03FFFh	
BA2	4 Kwords	02000h-02FFFh	
BA1	4 Kwords	01000h-01FFFh	
BA0	4 Kwords	00000h-00FFFh	



**PACKAGE DIMENSIONS**



# K8P1615UQB

# FLASH MEMORY

## PACKAGE DIMENSIONS

### 48-PIN LEAD PLASTIC THIN SMALL OUT-LINE PACKAGE TYPE(I)

